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**Suwada**

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(54) **ELECTRONIC PART, ELECTRONIC DEVICE, AND MANUFACTURING METHOD**

USPC ..... 257/532, 183, 295, E21.008, 499, 712,  
257/777, 784, E21.011; 438/125

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See application file for complete search history.

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**H01L 29/66** (2006.01)

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(2013.01); **H01L 23/481** (2013.01); **H01L**  
**23/5223** (2013.01); **H01L 23/5286** (2013.01);  
**H01L 23/642** (2013.01); **H01L 25/50**  
(2013.01); **H01L 24/13** (2013.01); **H01L 24/16**  
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**2224/131** (2013.01); **H01L 2224/16145**  
(2013.01); **H01L 2224/16227** (2013.01);  
(Continued)

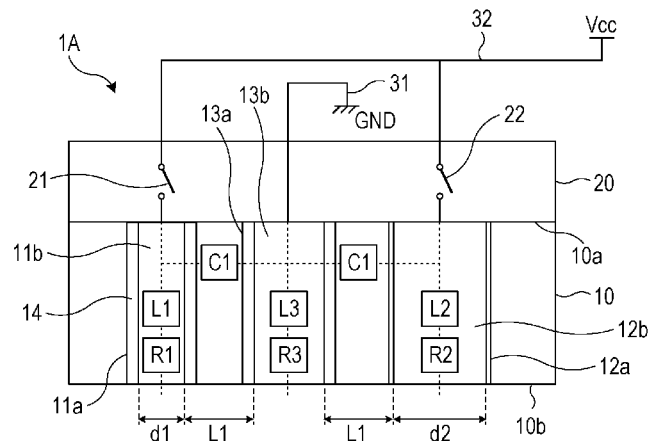
(57) **ABSTRACT**

An electronic part includes: a substrate; a first electrode configured to extend through the substrate and have a first opening size; a second electrode configured to extend through the substrate and have a second opening size; a switching section configured to switch between connection of the first electrode to a first power line and connection of the second electrode to the first power line; and a third electrode configured to extend through the substrate and be connected to a second power line different in potential from the first power line, a capacitance between the first and third electrodes and a capacitance between the second and third electrodes being different.

(58) **Field of Classification Search**

CPC . H01L 28/60; H01L 23/481; H01L 23/5222;  
H01L 23/5286; H01L 23/642; H01L 25/50;  
H01L 27/0629; H01L 2224/16; H01L  
2225/06513; H01L 2225/06517; H01L  
2225/06548; H01L 25/0657; H01L 21/76898;  
H01L 24/13; H01L 24/16; H01L 24/17;  
H01L 2224/131; H01L 2224/16145; H01L  
2224/16227; H01L 2224/17181; H01L  
23/5223; H01G 4/005

**11 Claims, 19 Drawing Sheets**



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*H01L 23/528* (2006.01)  
*H01L 25/00* (2006.01)  
*H01L 23/522* (2006.01)  
*H01L 21/768* (2006.01)  
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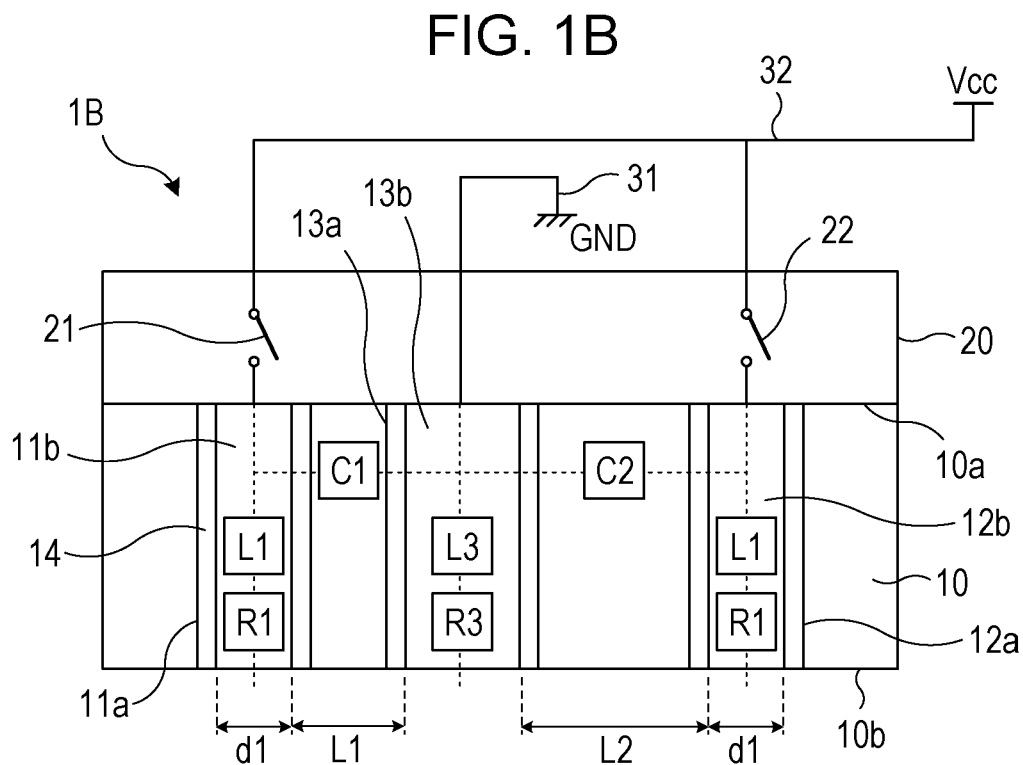


FIG. 2A

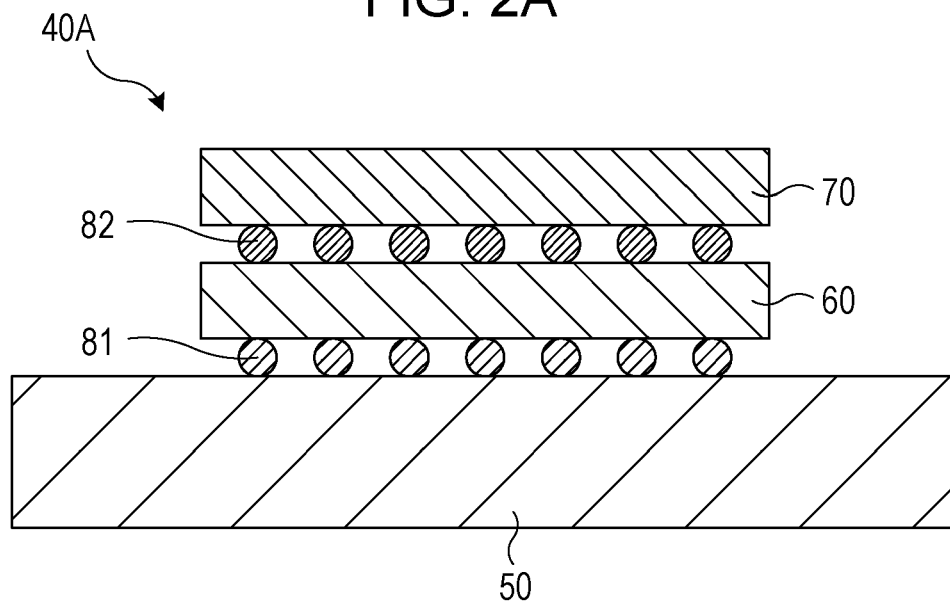


FIG. 2B

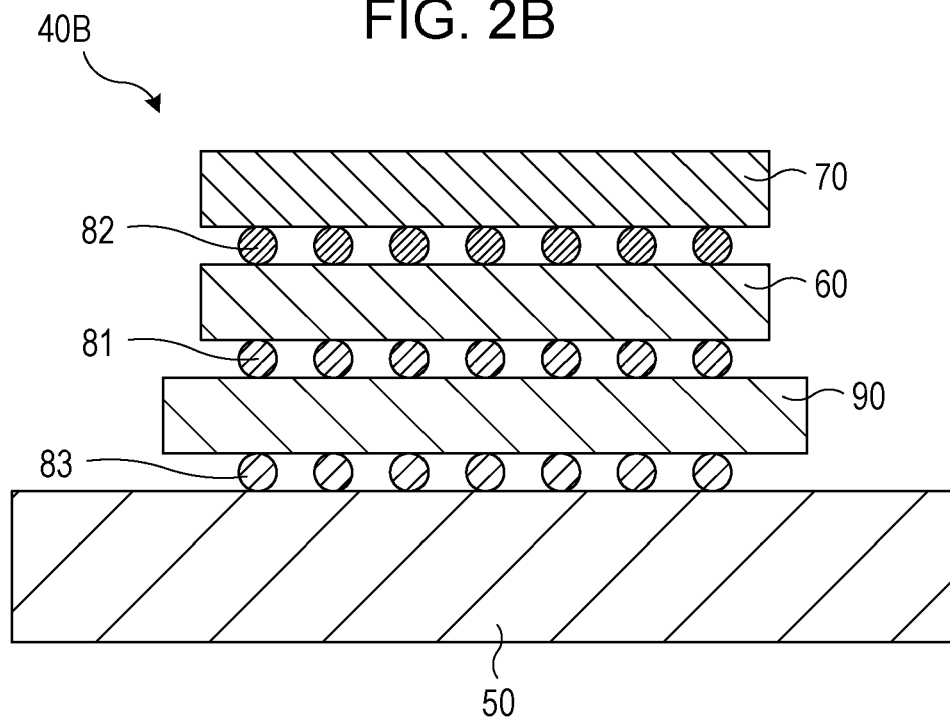


FIG. 3

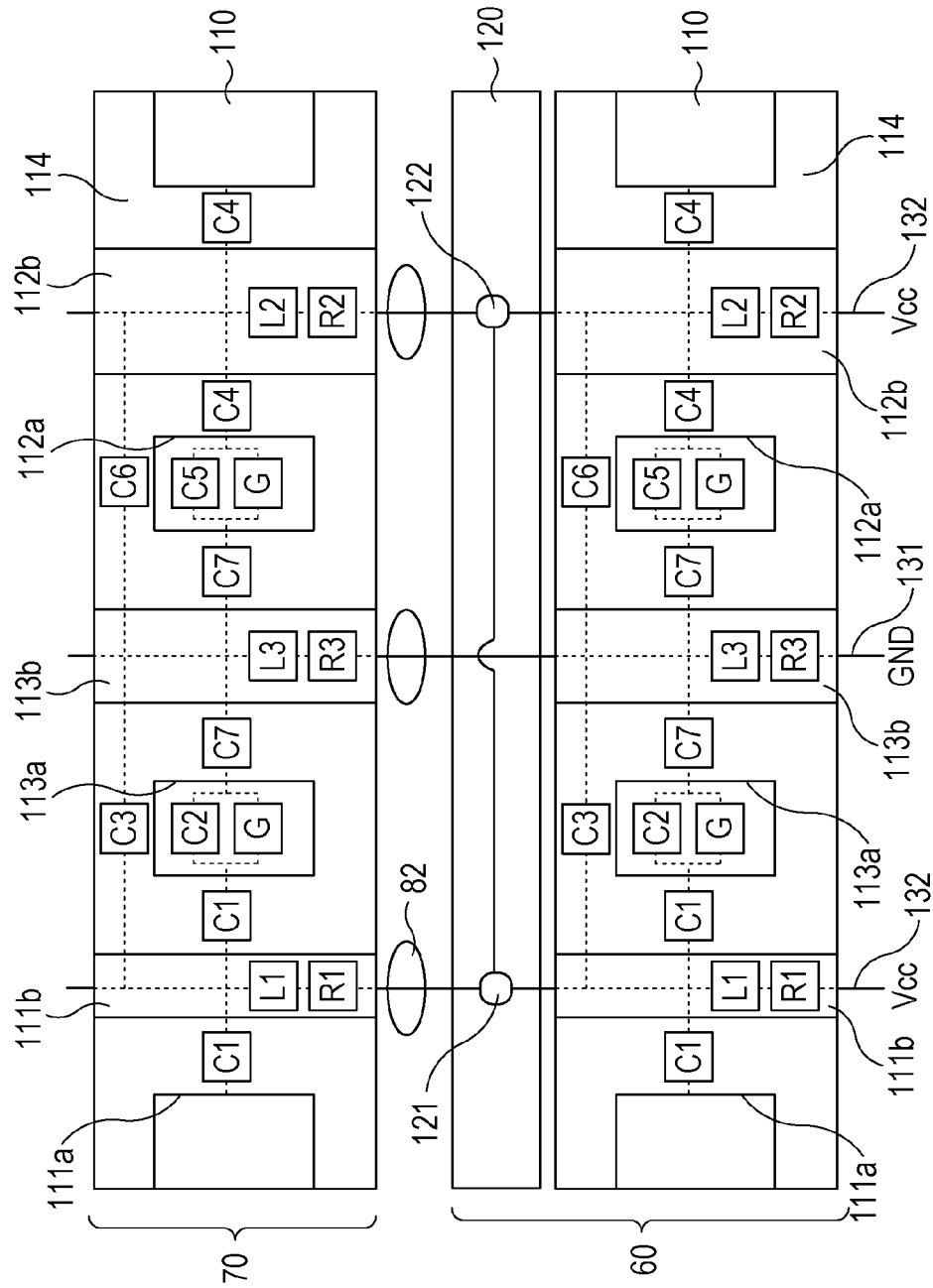


FIG. 4

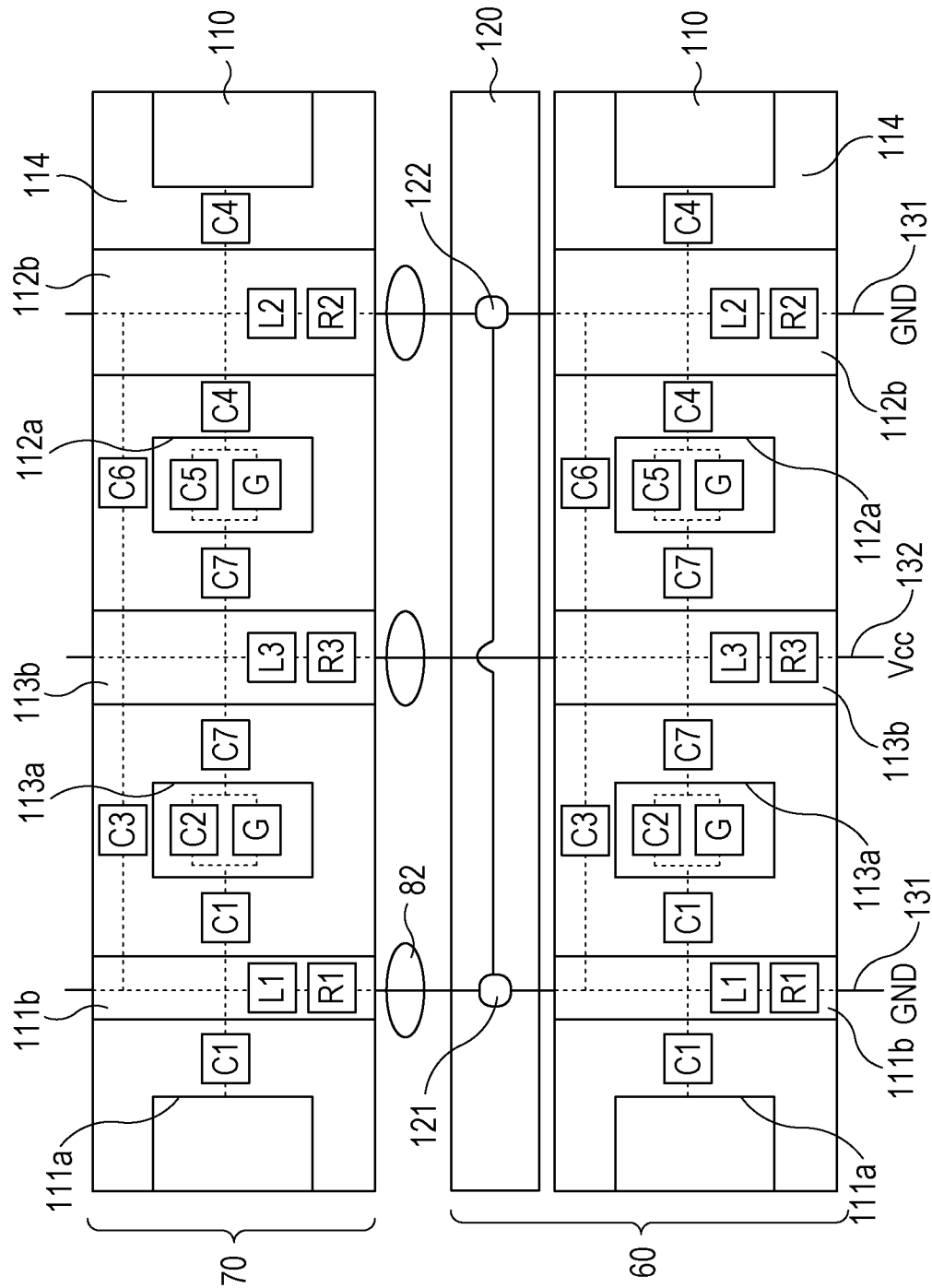


FIG. 5

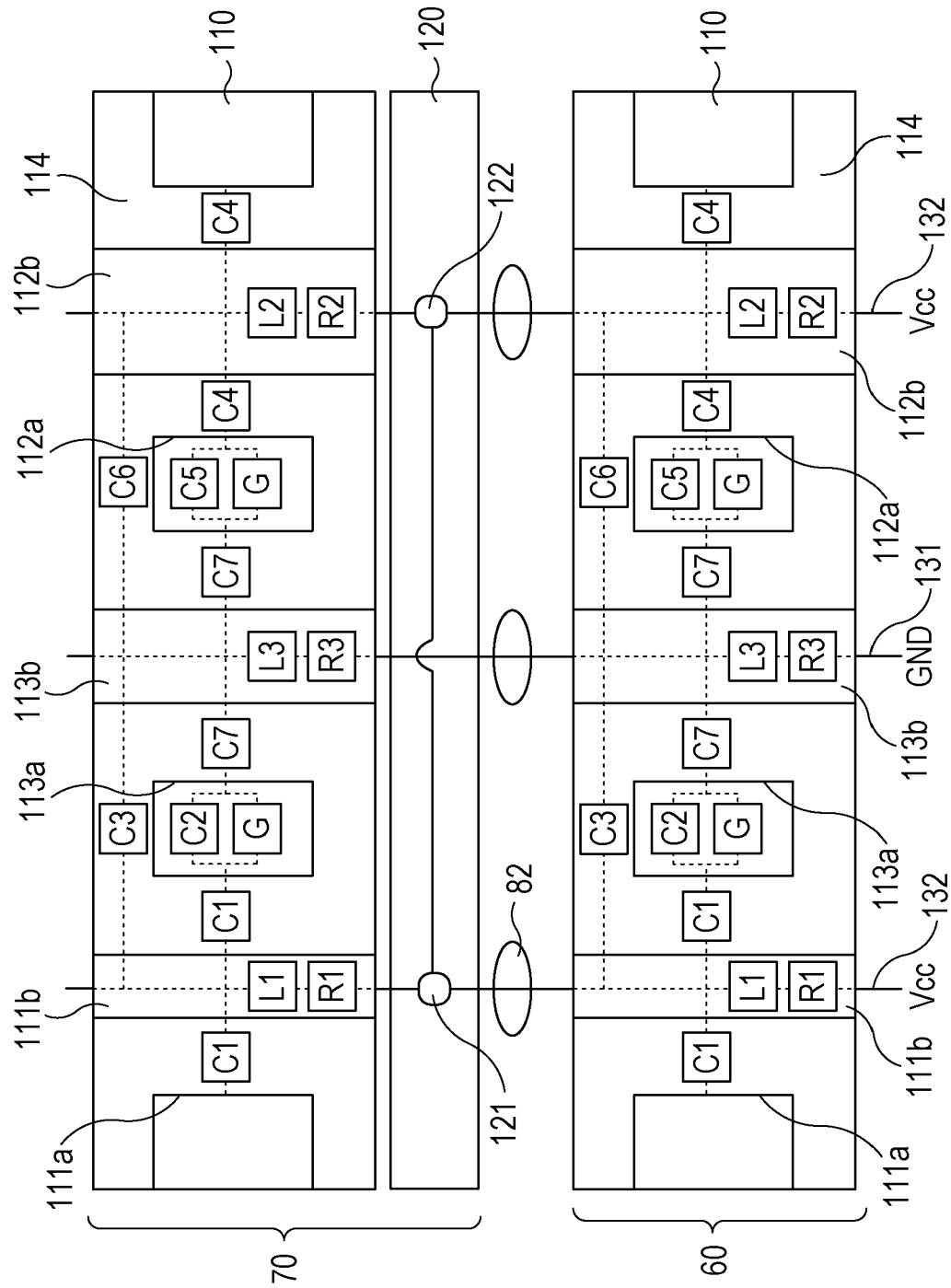


FIG. 6

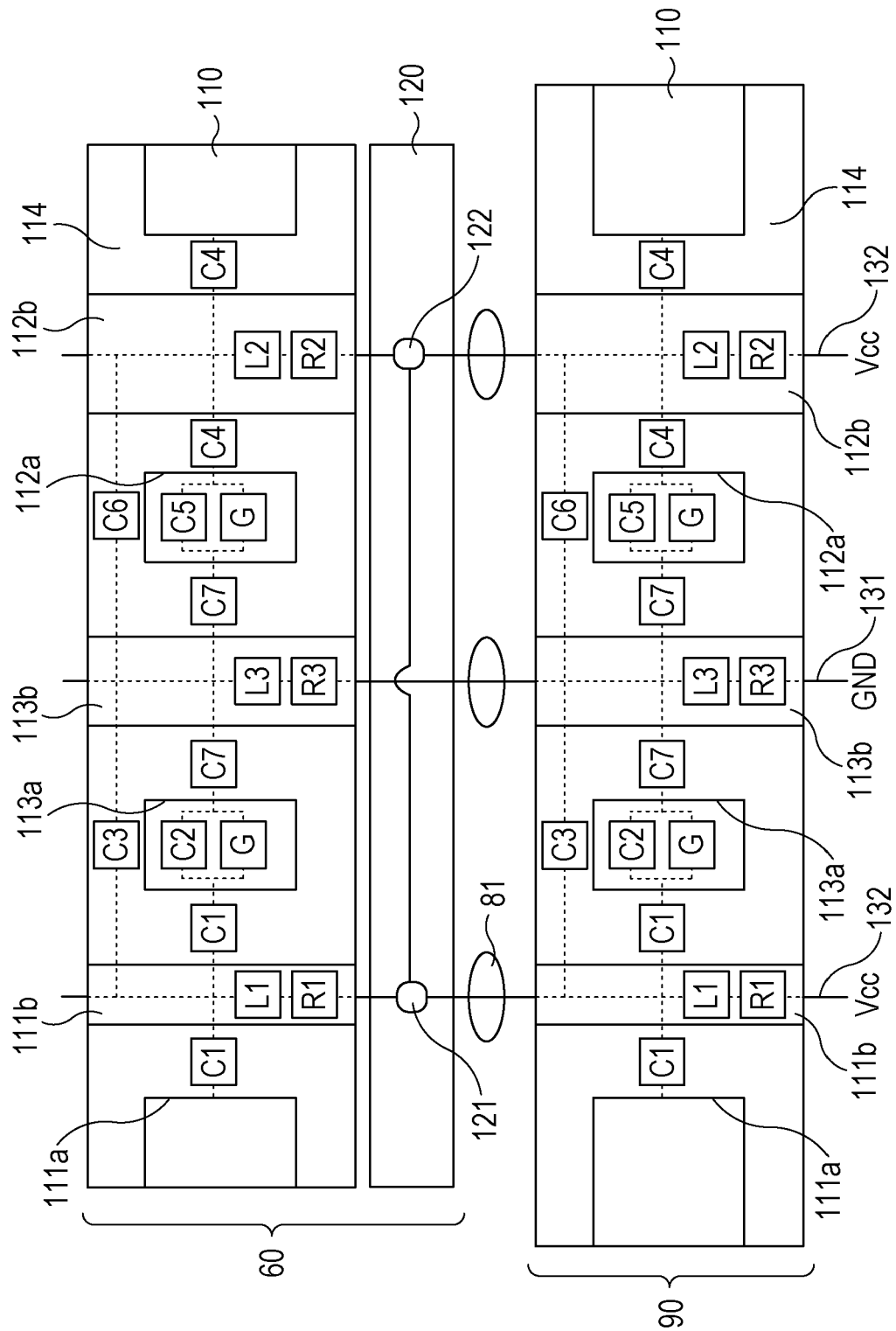




FIG. 7

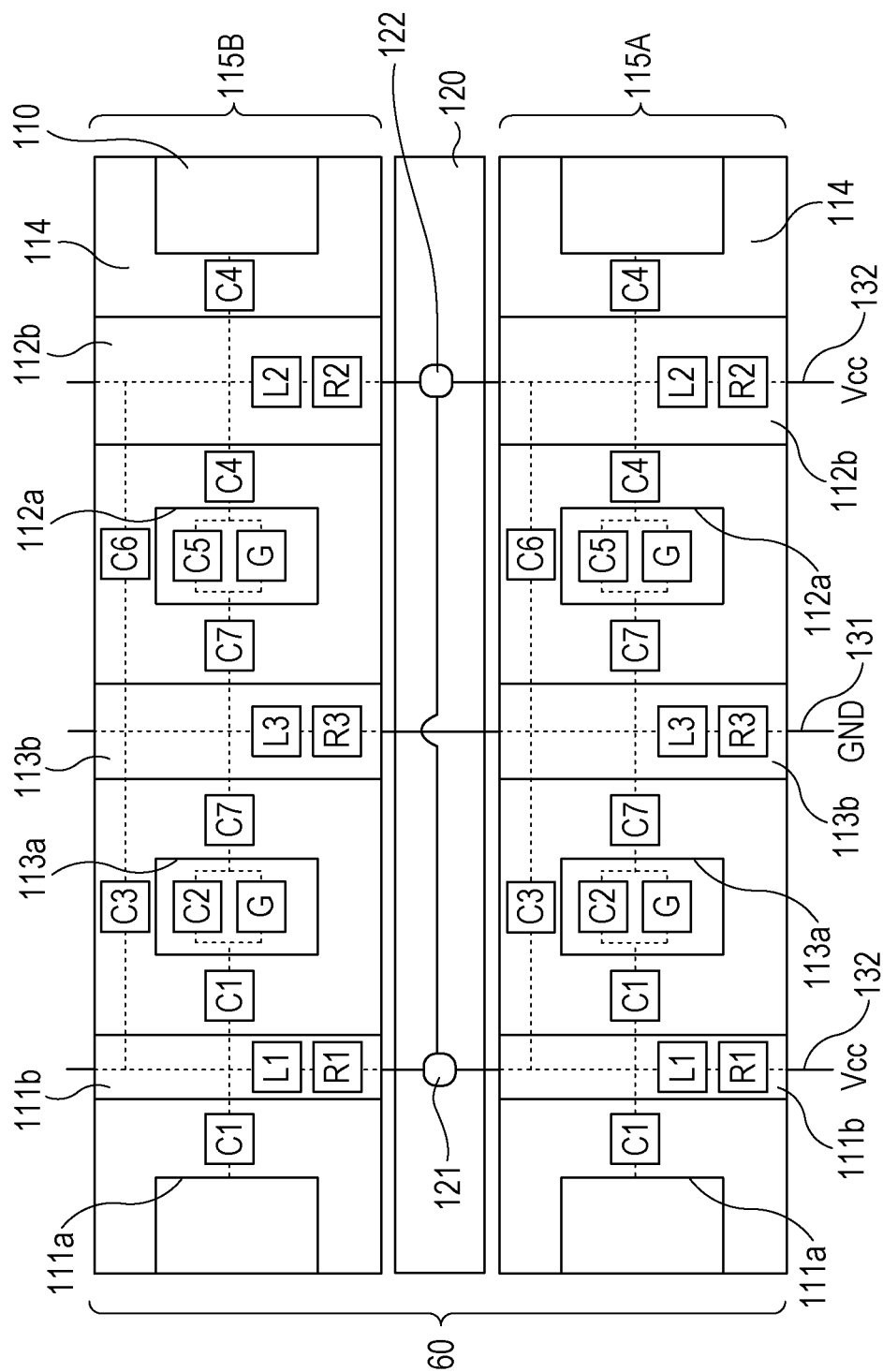


FIG. 8

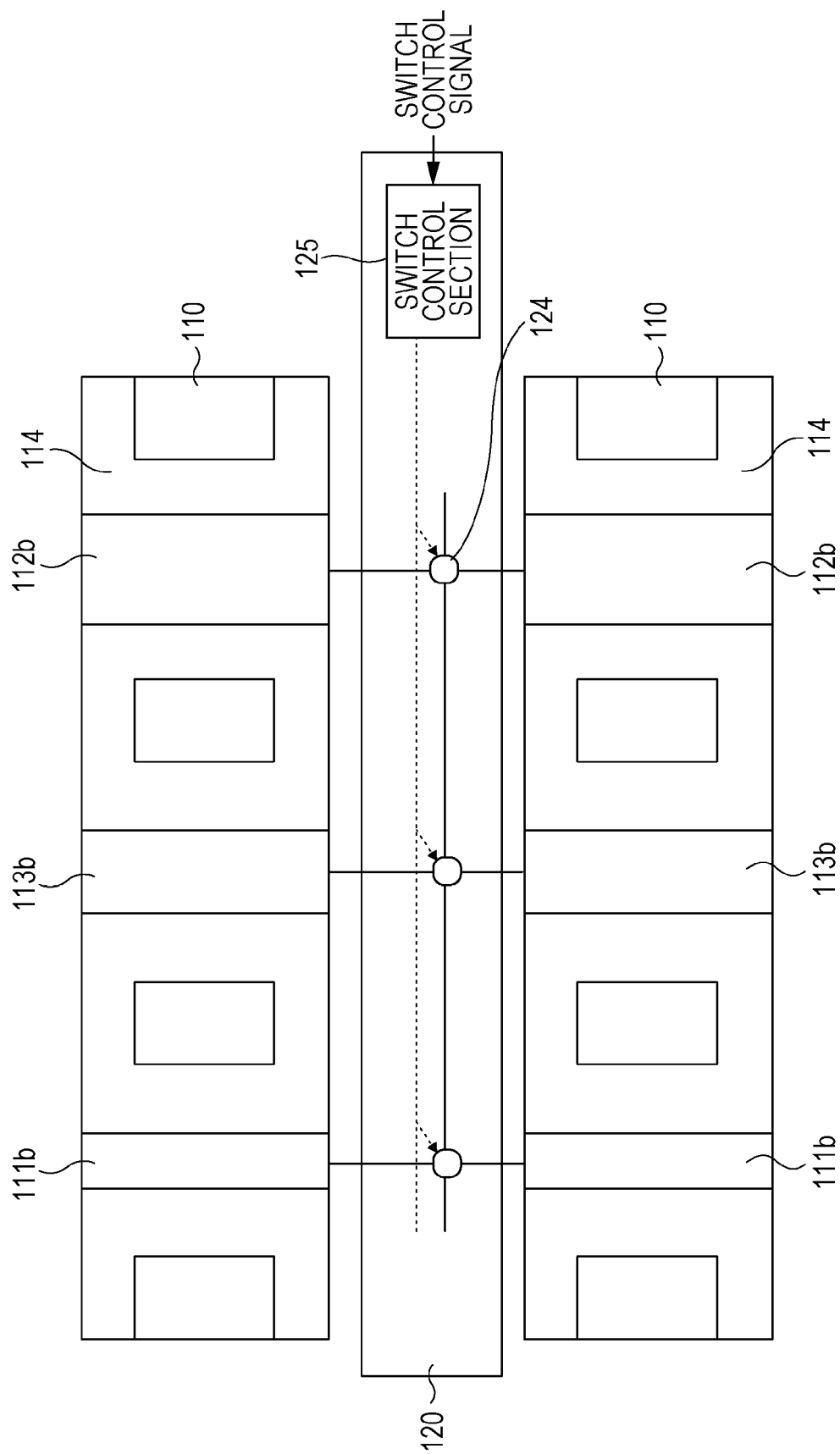


FIG. 9A

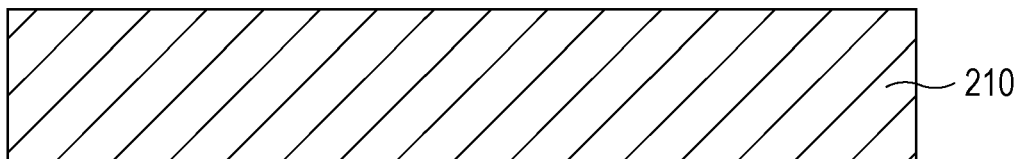


FIG. 9B

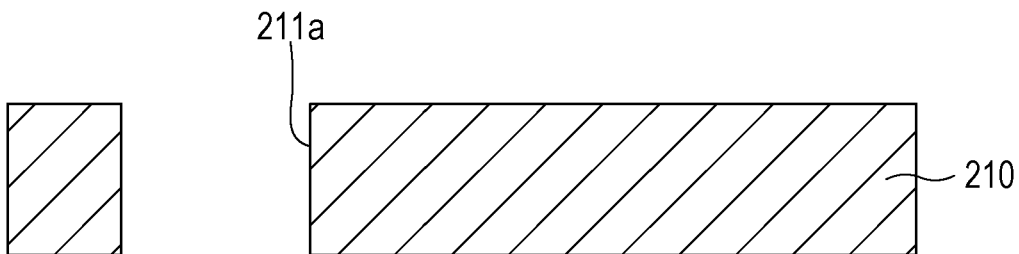


FIG. 9C

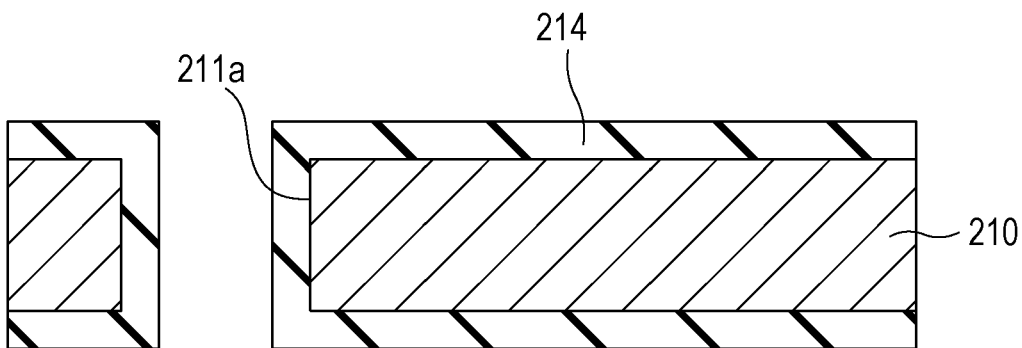


FIG. 10A

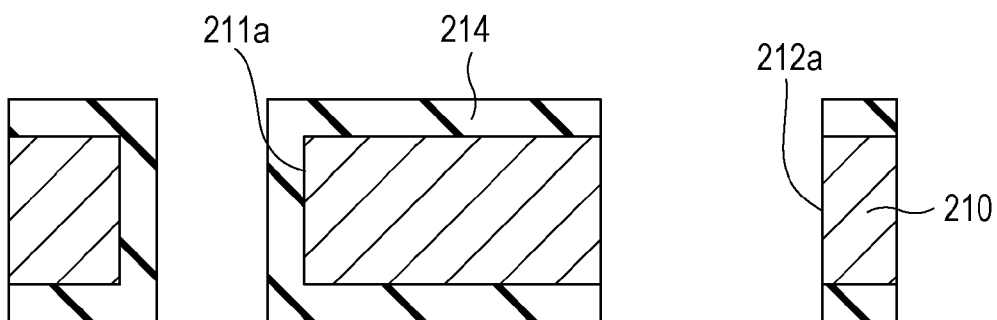


FIG. 10B

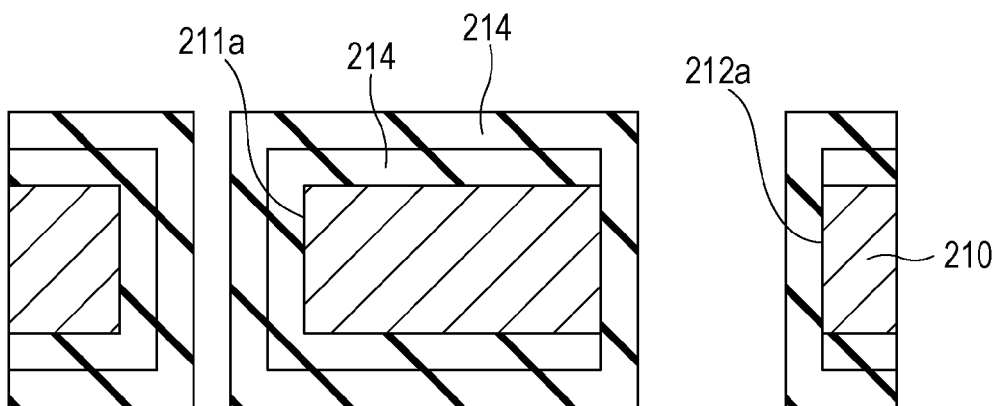


FIG. 10C

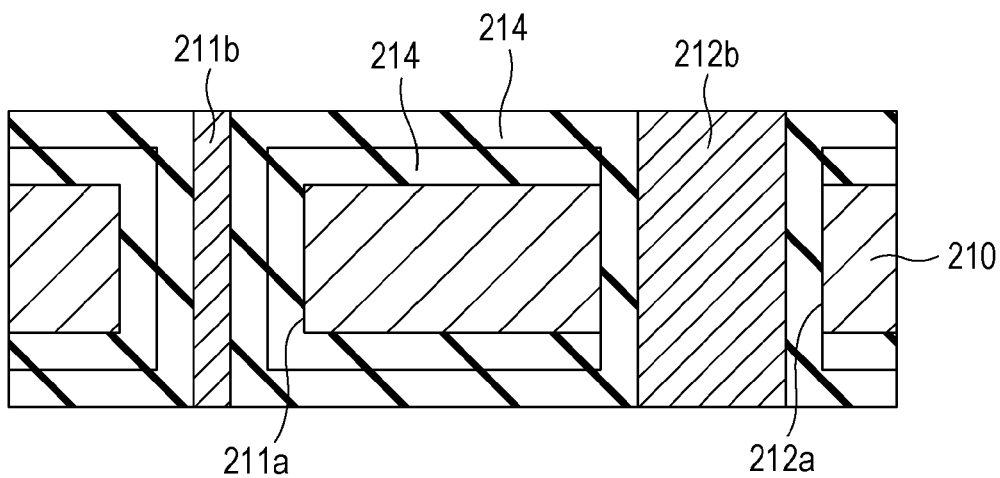


FIG. 11A

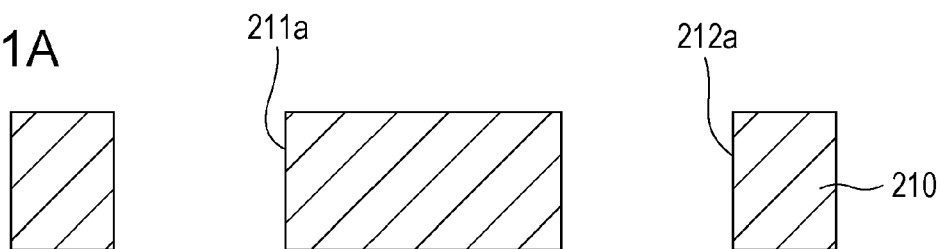


FIG. 11B

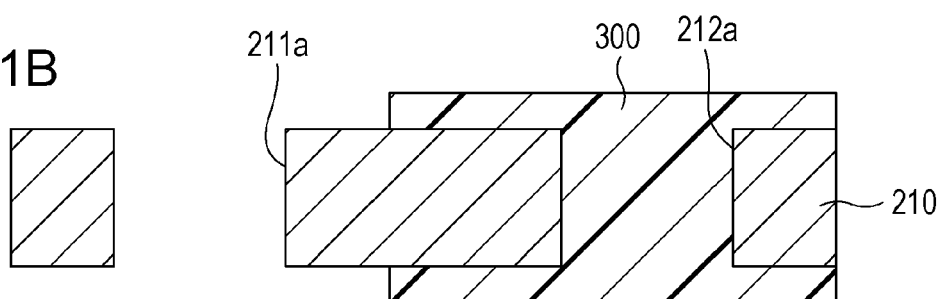


FIG. 11C

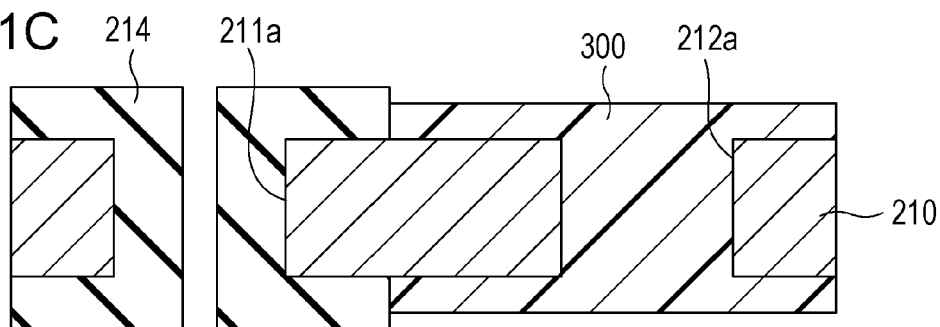


FIG. 11D

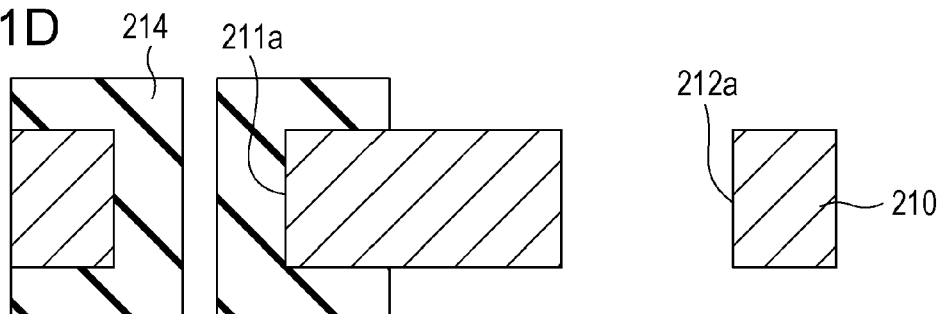


FIG. 12A

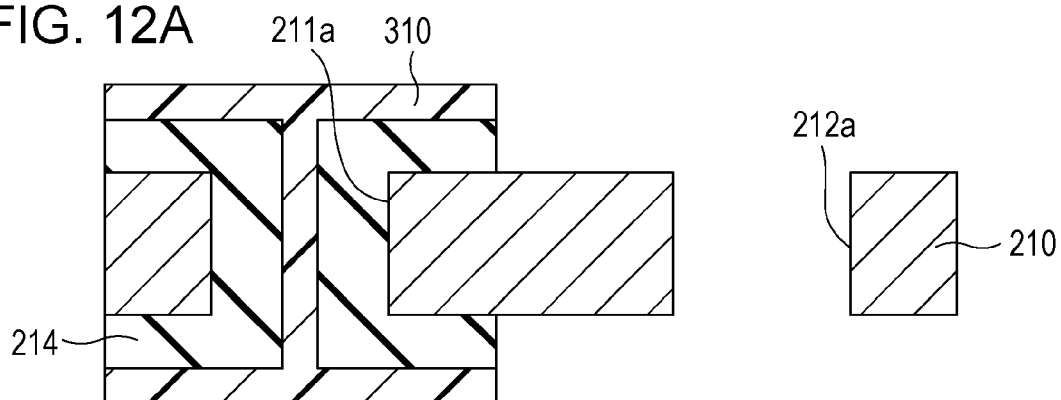


FIG. 12B

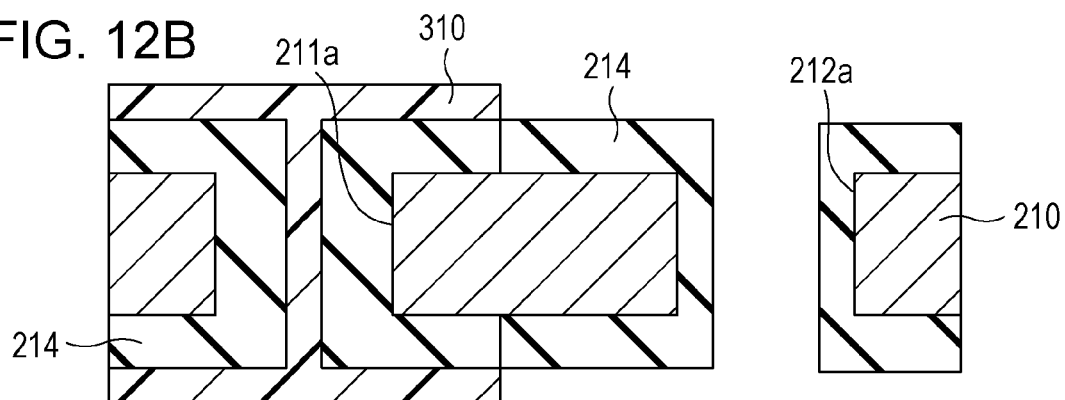


FIG. 12C

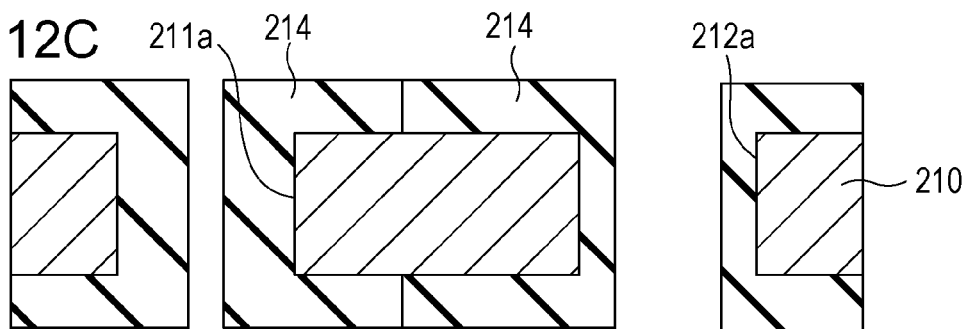


FIG. 12D

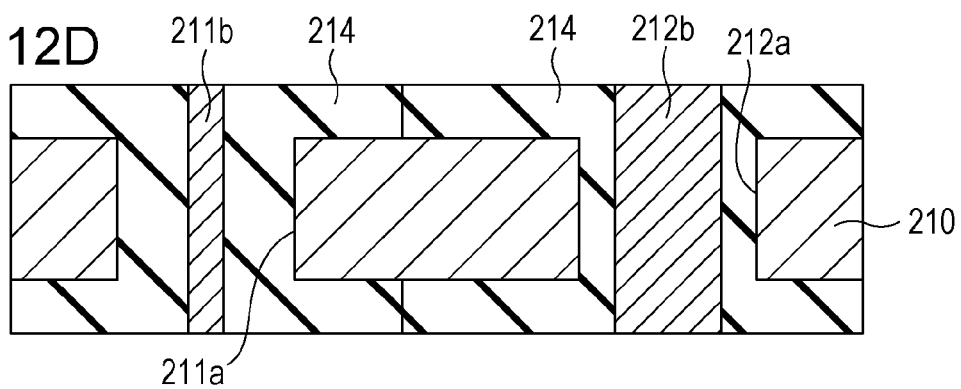


FIG. 13

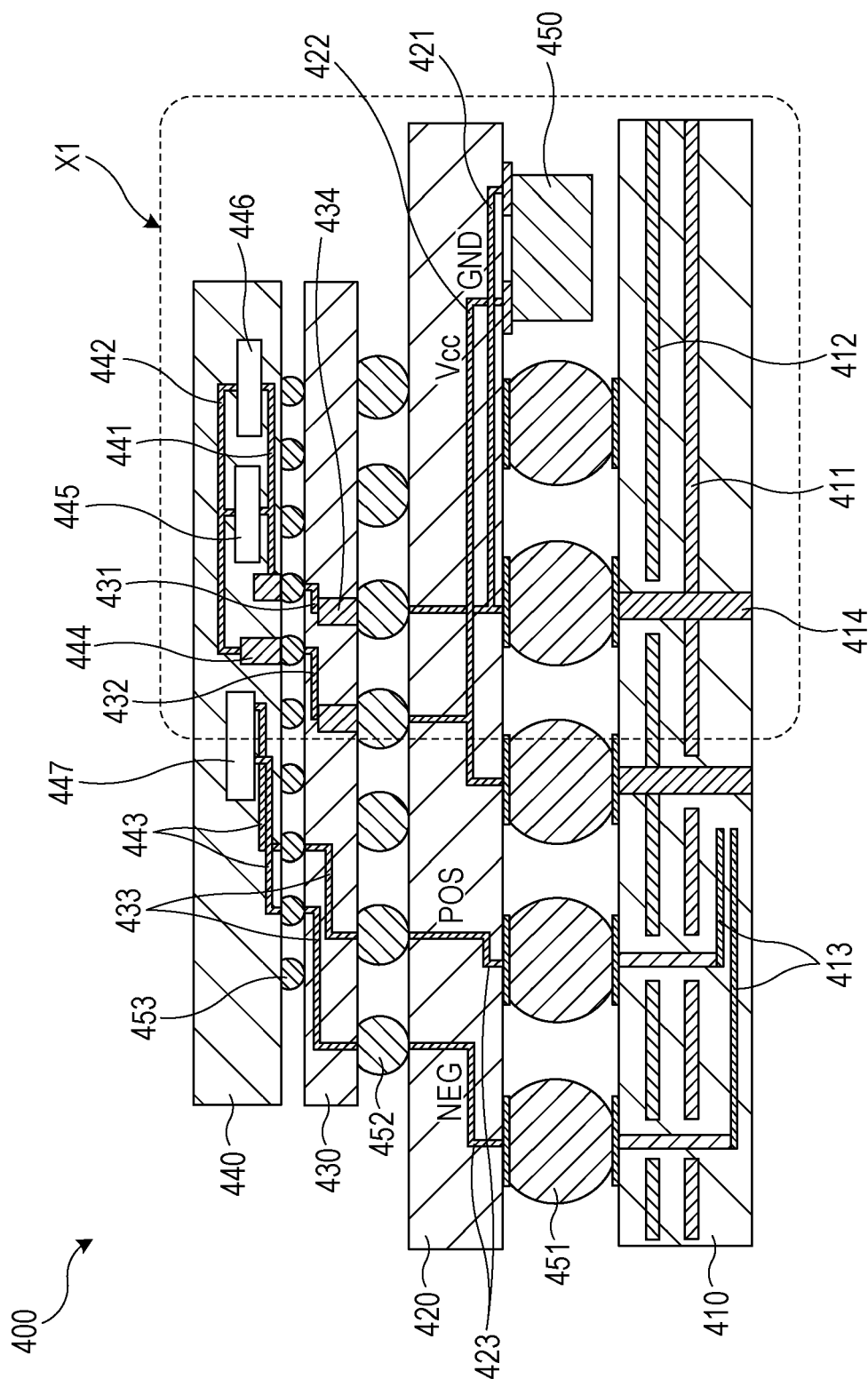


FIG. 14

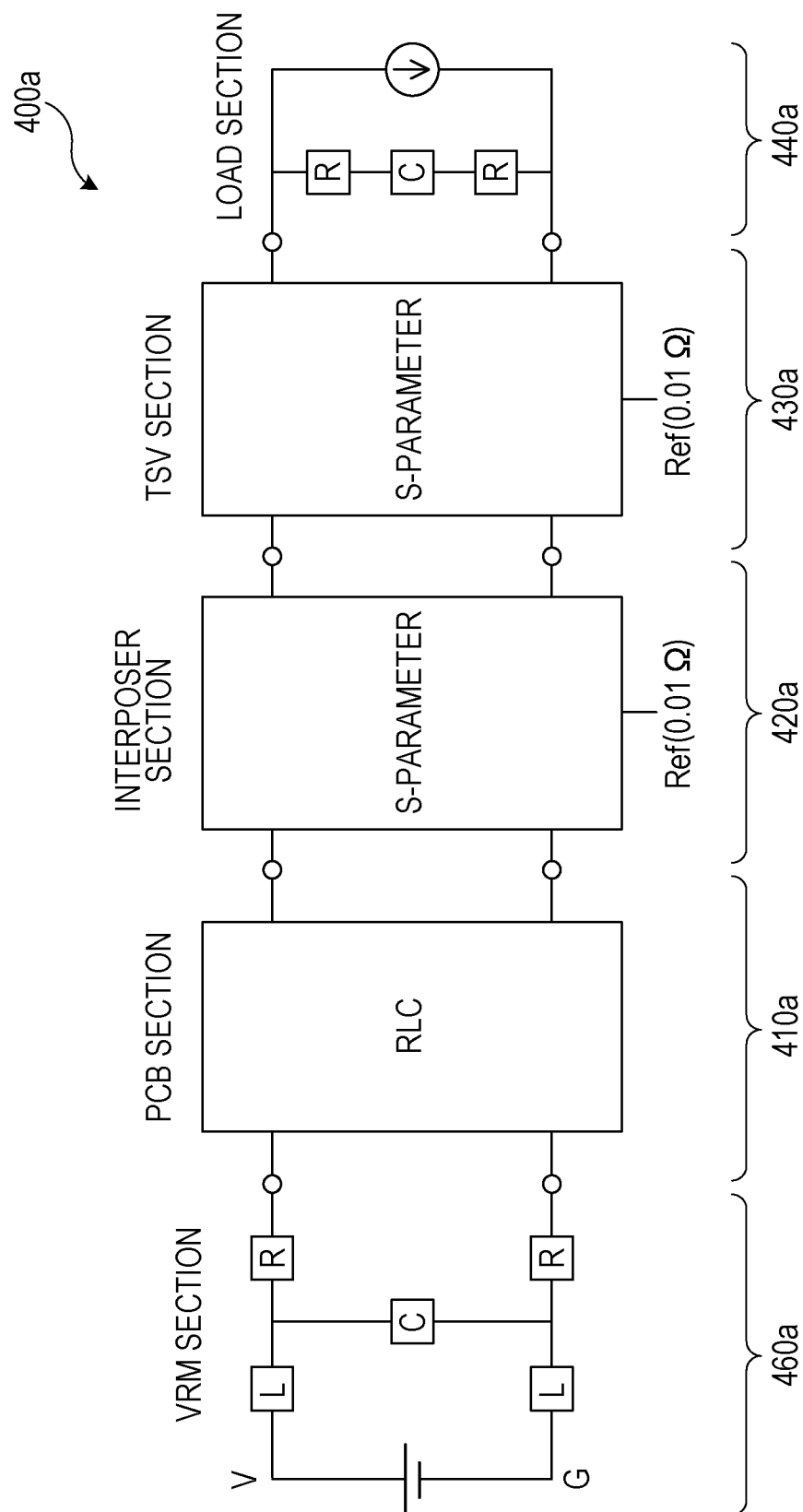




FIG. 15

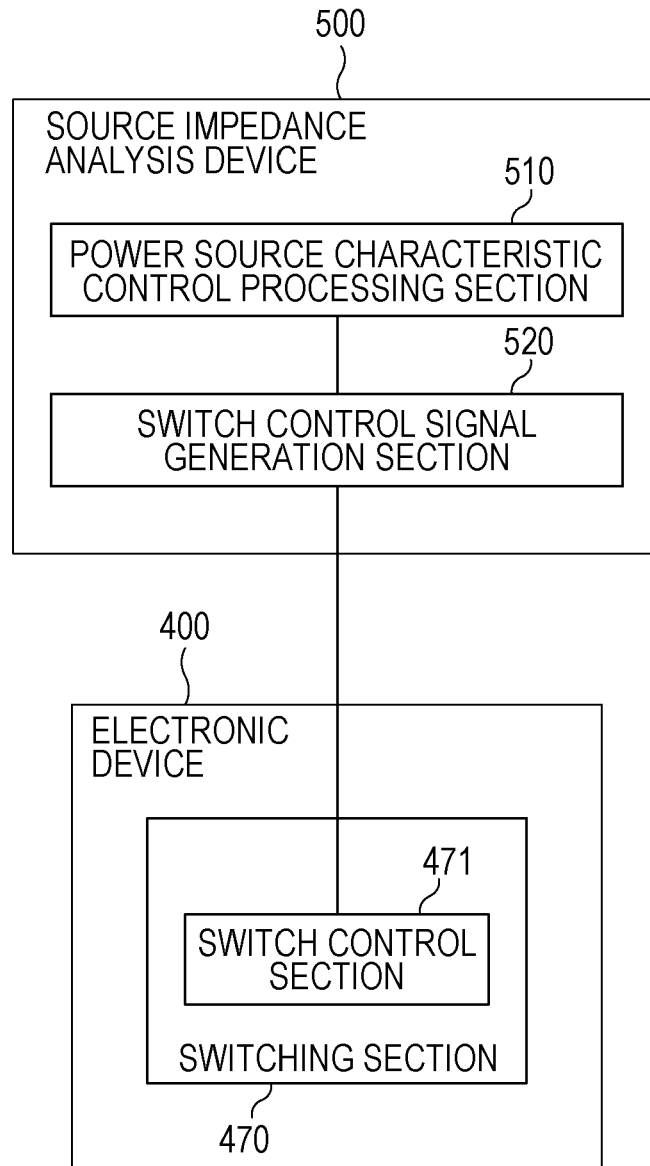


FIG. 16

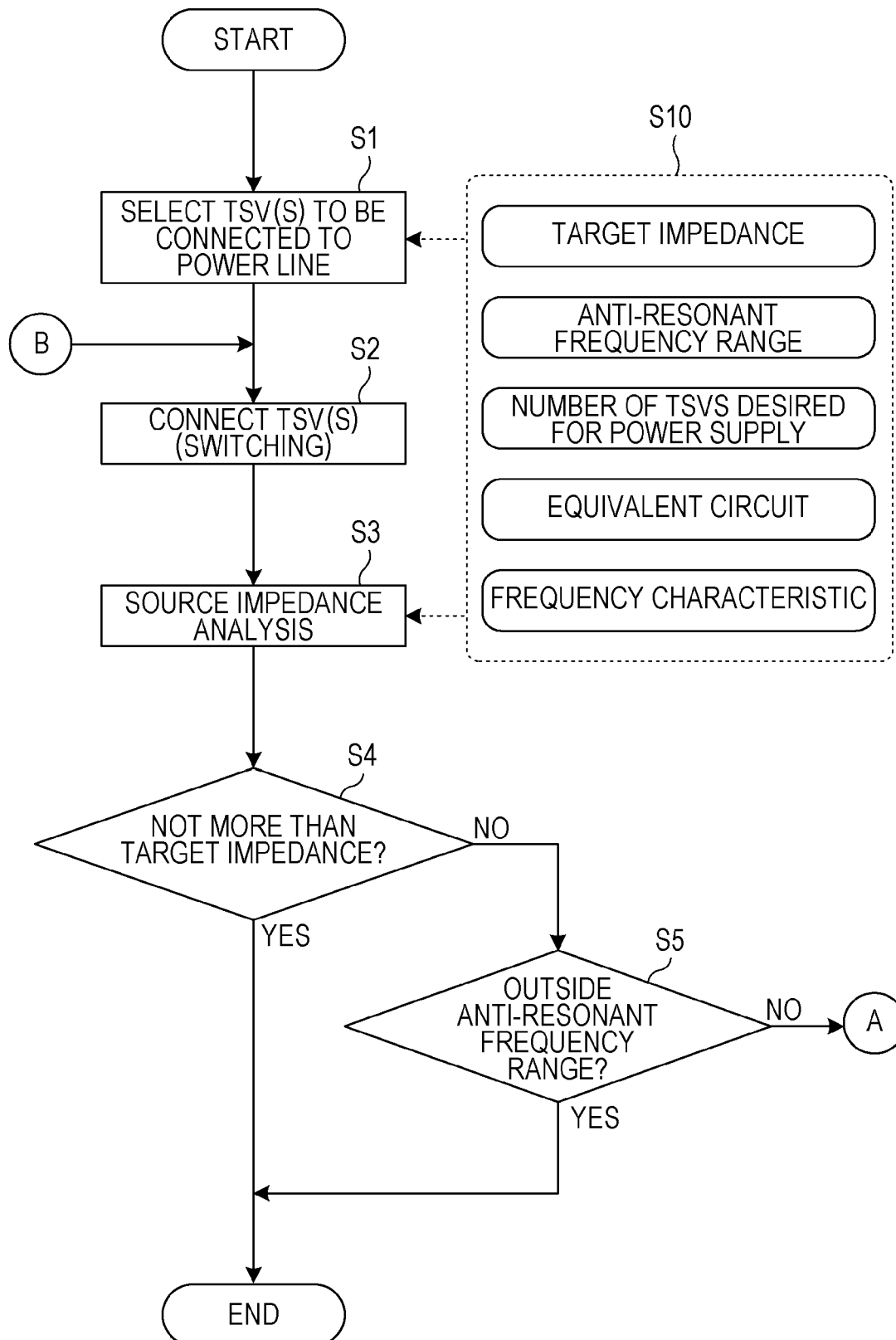


FIG. 17

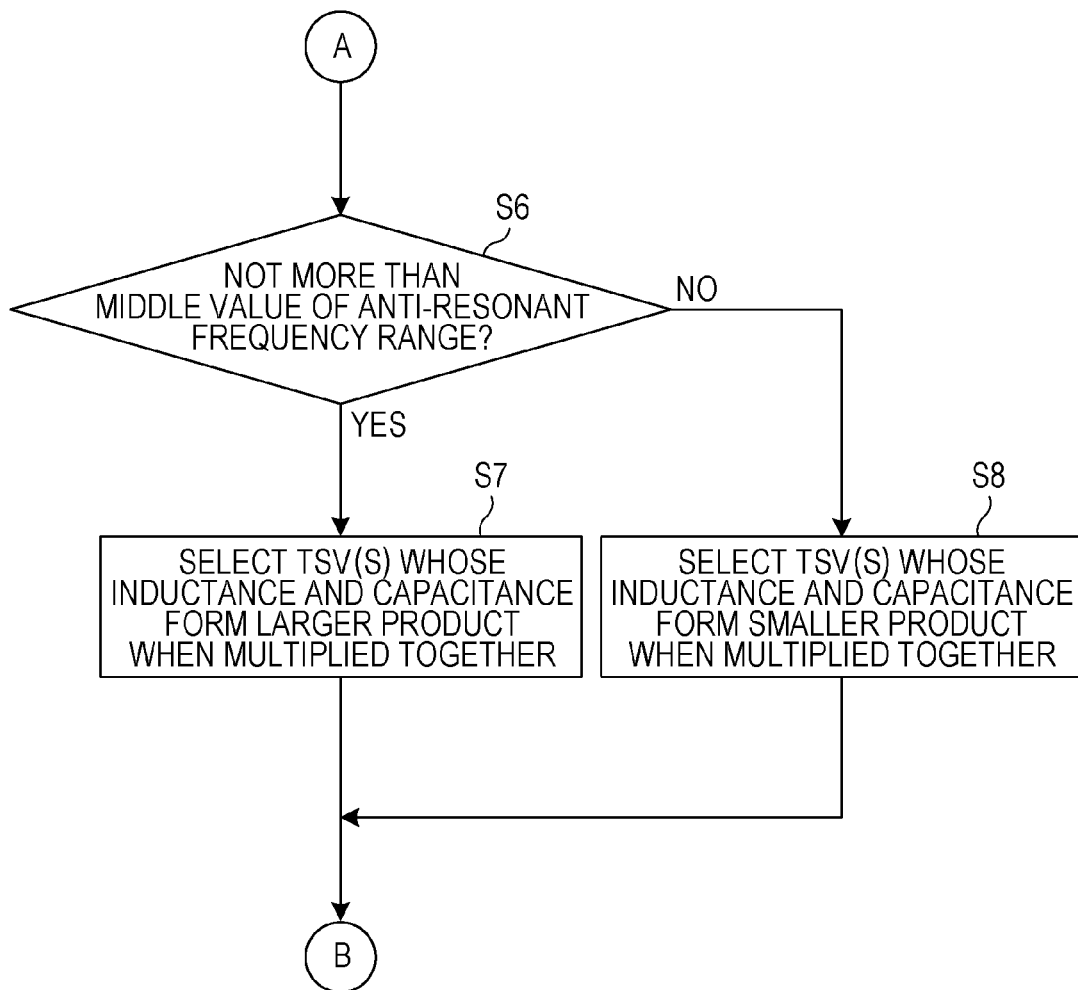


FIG. 18

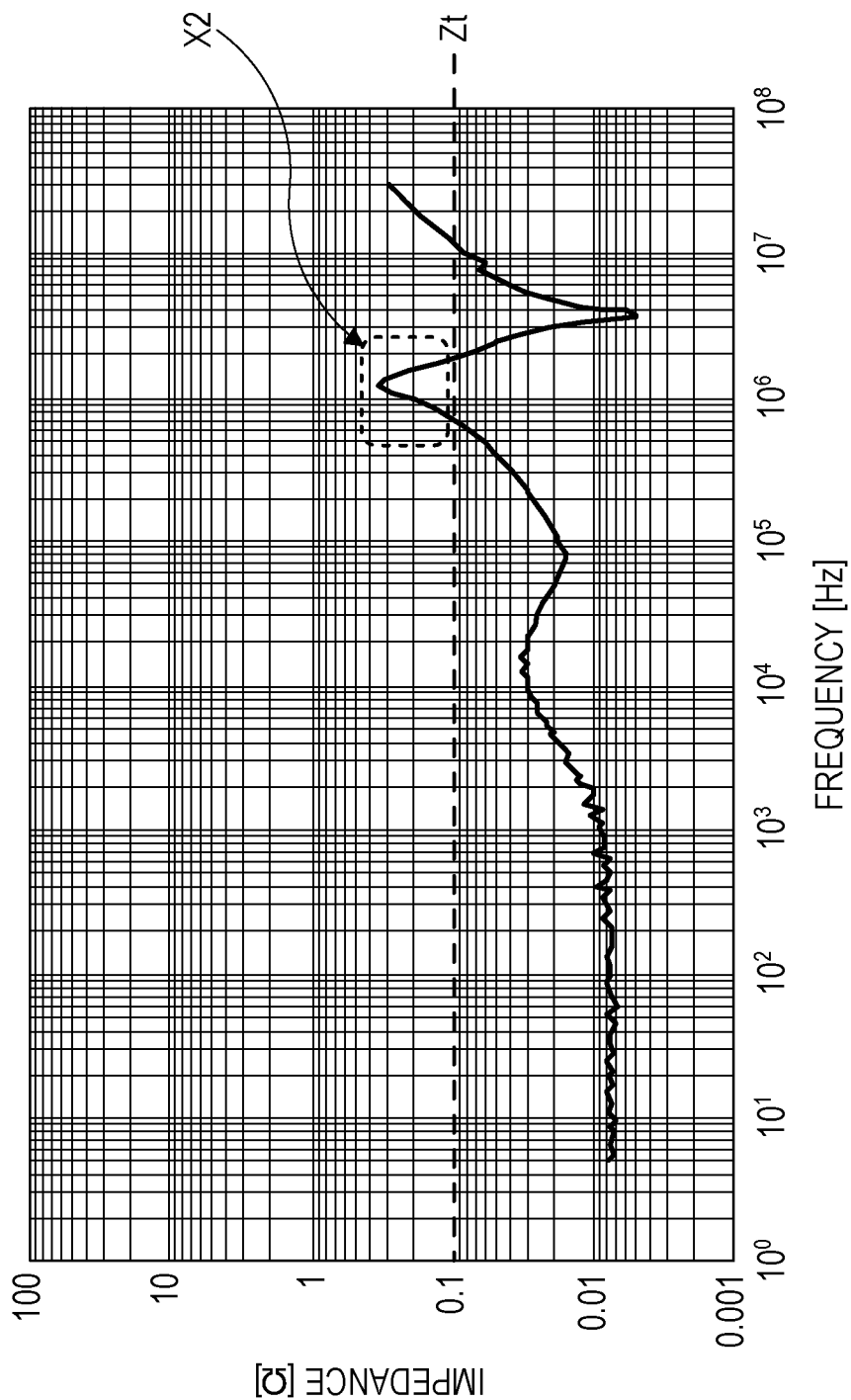
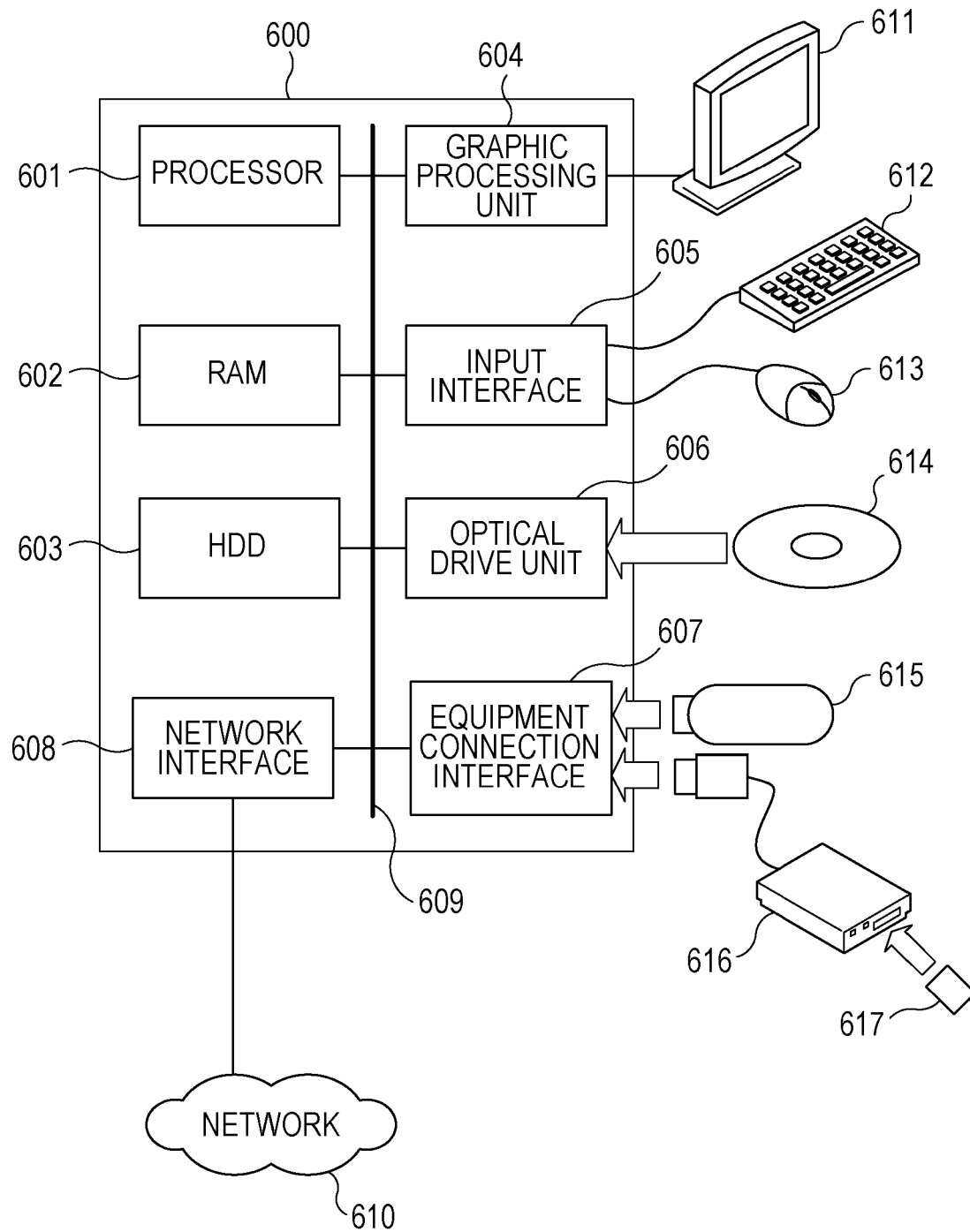


FIG. 19



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# ELECTRONIC PART, ELECTRONIC DEVICE, AND MANUFACTURING METHOD

## CROSS-REFERENCE TO RELATED APPLICATION

This application is based upon and claims the benefit of priority of the prior Japanese Patent Application No. 2014-145893, filed on Jul. 16, 2014, the entire contents of which are incorporated herein by reference.

## FIELD

The embodiments discussed herein are related to an electronic part, an electronic device, and a method for manufacturing the electronic device.

## BACKGROUND

There is known a technique for providing a bypass capacitor (also referred to as a decoupling capacitor or the like) on a power line of an electronic part, such as a semiconductor chip, or an electronic device including an electronic part in terms of power integrity. A technique is known for providing a film-like capacitor between stacked semiconductor chips, besides a technique for providing a chip capacitor as a bypass capacitor. In addition, a technique is known for alternately arranging connection conductors, each connecting power lines of a stacked semiconductor package, and connection conductors, each connecting ground lines, to give a capacitance between adjacent ones of the connection conductors.

Japanese Patent Publications Nos. 2005-244068 and 2009-182087 are examples of related art.

Under the conventional technology, the capacitance and layout of a bypass capacitor may be determined by the configuration of an electronic part or an electronic device, and it may be difficult to achieve satisfactory power integrity for each individual electronic part or electronic device. A necessity may arise for redesign and remanufacture of each individual electronic part or electronic device with the aim of achieving satisfactory power integrity.

## SUMMARY

According to an aspect of the embodiments, an electronic part includes: a substrate; a first electrode configured to extend through the substrate and have a first opening size; a second electrode configured to extend through the substrate and have a second opening size; a switching section configured to switch between connection of the first electrode to a first power line and connection of the second electrode to the first power line; and a third electrode configured to extend through the substrate and be connected to a second power line different in potential from the first power line, a capacitance between the first and third electrodes and a capacitance between the second and third electrodes being different.

The object and advantages of the invention will be realized and attained by means of the elements and combinations particularly pointed out in the claims.

It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are not restrictive of the invention, as claimed.

## BRIEF DESCRIPTION OF DRAWINGS

FIGS. 1A and 1B are diagrams illustrating examples of an electronic part according to a first embodiment;

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FIGS. 2A and 2B are diagrams illustrating examples of an electronic device according to a second embodiment;

FIG. 3 is a diagram (part 1) illustrating a first example of semiconductor chips according to the second embodiment;

FIG. 4 is a diagram (part 2) illustrating the first example of the semiconductor chips according to the second embodiment;

FIG. 5 is a diagram illustrating a second example of the semiconductor chips according to the second embodiment;

FIG. 6 is a diagram illustrating a third example of the semiconductor chips according to the second embodiment;

FIG. 7 is a diagram illustrating a fourth example of the semiconductor chips according to the second embodiment;

FIG. 8 is a diagram for explaining an example of a switching section according to the second embodiment;

FIGS. 9A, 9B, and 9C are diagrams (part 1) for explaining an example of a substrate formation method according to a third embodiment;

FIGS. 10A, 10B, and 10C are diagrams (part 2) for explaining the example of the substrate formation method according to the third embodiment;

FIGS. 11A, 11B, 11C, and 11D are diagrams (part 1) for explaining a different example of the substrate formation method according to the third embodiment;

FIGS. 12A, 12B, 12C, and 12D are diagrams (part 2) for explaining the different example of the substrate formation method according to the third embodiment;

FIG. 13 is a diagram illustrating an example of an electronic device according to a fourth embodiment;

FIG. 14 is a diagram illustrating an example of an electronic device model according to the fourth embodiment;

FIG. 15 is a diagram illustrating an example of a source impedance analysis device used for power source characteristic control processing according to the fourth embodiment;

FIG. 16 is a chart (part 1) illustrating an example of a power source characteristic control processing flow according to the fourth embodiment;

FIG. 17 is a chart (part 2) illustrating the example of the power source characteristic control processing flow according to the fourth embodiment;

FIG. 18 is a graph illustrating an example of a source impedance characteristic; and

FIG. 19 is a diagram illustrating an example of the hardware configuration of a computer used as a source impedance analysis device.

## DESCRIPTION OF EMBODIMENTS

A first embodiment will be described first.

FIGS. 1A and 1B are diagrams illustrating examples of an electronic part according to a first embodiment. FIGS. 1A and 1B schematically illustrate examples of the configuration of a main portion of the electronic part according to the first embodiment.

An electronic part 1A illustrated in FIG. 1A is, for example, a semiconductor chip (semiconductor element). The electronic part 1A includes a substrate 10 and a switching section 20.

For example, a semiconductor substrate of silicon (Si) or the like may be used as the substrate 10. A compound semiconductor substrate of silicon germanium (SiGe), silicon carbide (SiC), gallium nitride (GaN) or the like may also be used as the substrate 10.

The substrate 10 has a through-hole extending between a principal surface 10a and a principal surface 10b thereof. By

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way of example, the substrate **10** has three through-holes, a through-hole **11a**, a through-hole **12a**, and a through-hole **13a**.

An electrode **11b**, an electrode **12b**, and an electrode **13b** for electrical continuity between the principal surfaces **10a** and **10b** of the substrate **10** are provided in the through-holes **11a**, **12a**, and **13a**, respectively. Every type of conductive material may be used as the materials for the electrodes **11b**, **12b**, and **13b**. For example, copper (Cu) or a material based on Cu may be used. Note that if the electrodes **11b**, **12b**, and **13b** are provided in the substrate **10** of Si, the electrodes **11b**, **12b**, and **13b** may also be referred to as through silicon vias (TSVs).

Side surfaces of the electrodes **11b**, **12b**, and **13b** are covered with respective insulating films (dielectric films) **14** and are electrically separated from inner surfaces of the through-holes **11a**, **12a**, and **13a** of the substrate **10**.

The electrodes **11b**, **12b**, and **13b** of the electronic part **1A** are electrically connected to a circuit (load) including a transistor or the like (not illustrated). The electronic part **1A** may be electrically connected to a different electronic part (a semiconductor chip, an interposer, a printed circuit board, or the like) via the electrodes **11b**, **12b**, and **13b**.

The diameters (opening sizes) of the through-holes **11a**, **12a**, and **13a** may be equal to or different from each other. FIG. 1A illustrates the through-holes **11a**, **12a**, and **13a** having opening sizes different from each other.

The electrodes **11b**, **12b**, and **13b** are provided in the above-described through-holes **11a**, **12a**, and **13a**, respectively, via the insulating films **14**. FIG. 1A illustrates a case where the electrode **11b** is the smallest in diameter, followed by the electrode **13b** and the electrode **12b** in this order (a diameter of the electrode **11b** < a diameter of the electrode **12b**).

The distance between the electrodes **11b** and **13b** (the distance between outer edges of the electrodes **11b** and **13b**) and the distance between the electrodes **12b** and **13b** (the distance between outer edges of the electrodes **12b** and **13b**) may be equal to or different from each other. FIG. 1A illustrates a case where the distance between the electrodes **11b** and **13b** and the distance between the electrodes **12b** and **13b** are equal to each other (distances **L1**).

The thicknesses of the insulating films **14** provided at the side surfaces of the electrodes **11b**, **12b**, and **13b** may be equal to or different from each other. FIG. 1A illustrates a case where the insulating films **14** different in thickness are provided at the side surfaces of the electrodes **11b** and **12b**.

In the substrate **10** having the electrodes **11b**, **12b**, and **13b** with diameters as illustrated in FIG. 1A, the electrodes **11b**, **12b**, and **13b** have respective different resistances **R1** to **R3** and respective different inductances **L1** to **L3**. Note that a capacitance between the electrodes **11b** and **13b** and a capacitance between the electrodes **12b** and **13b** are assumed to be equal to each other in the example in FIG. 1A (a capacitance **C1**).

For example, in the electronic part **1A** illustrated in FIG. 1A, the electrode **13b** is electrically connected to a power line (GND line) **31** which is set at a ground potential GND. The electrodes **11b** and **12b** are configured to be electrically connectable to a power line (power supply line) **32** which is set at a power potential **Vcc**. Switching between connection of the electrode **11b** to the power supply line **32** and disconnection of the electrode **11b** from the power supply line **32** and switching between connection of the electrode **12b** to the power supply line **32** and disconnection of the electrode **12b** from the power supply line **32** are performed by a switching section **20**.

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The switching section **20** includes, for example, a switch **21** and a switch **22**. The switch **21** switches between connection of the electrode **11b** to the power supply line **32** and disconnection of the electrode **11b** from the power supply line **32**, and the switch **22** switches between connection of the electrode **12b** to the power supply line **32** and disconnection of the electrode **12b** from the power supply line **32**. Whether the switches **21** and **22** are turned on or off (the electrodes **11b** and **12b** are connected to or disconnected from the power supply line **32**) may be controlled using, for example, a control section (switch control section) which is connected to the switches **21** and **22**.

For example, a semiconductor switch which is formed using a metal oxide semiconductor (MOS) transistor or the like may be used as each of the switches **21** and **22**. For example, when the electronic part **1A** is a semiconductor chip, a semiconductor switch may be implemented using a semiconductor substrate (the substrate **10**) used in the semiconductor chip and a wiring layer which is provided on the semiconductor substrate.

As each of the switch **21** and the switch **22**, a mechanical switch which is provided at a junction of the electronic part **1A** with a different electronic part (a semiconductor chip, an interposer, a printed circuit board, or the like) or a power line (the GND line **31** or the power supply line **32**) may be used besides the above-described semiconductor switch.

In the electronic part **1A** with the above-described configuration, it is possible to connect the electrode **11b** to the power supply line **32** and connect the electrode **12b** to the power supply line **32**, using the switches **21** and **22** of the switching section **20**. It is also possible to connect both the electrodes **11b** and **12b** to the power supply line **32** using the switches **21** and **22** of the switching section **20**.

In the electronic part **1A**, the electrodes **11b** and **12b** are different in diameter, as in the example of FIG. 1A. The difference in diameter between the electrodes **11b** and **12b** makes component values of the resistance **R1** and the inductance **L1** in the electrode **11b** different from component values of the resistance **R2** and the inductance **L2** in the electrode **12b**.

For this reason, in the electronic part **1A**, a circuit configuration (equivalent circuit) including the power supply line **32** and the GND line **31** varies with the form of connection of the electrodes **11b** and **12b** to the power supply line **32** in the switching section **20**. A change in the circuit configuration within the electronic part **1A** changes a source impedance and a resonant frequency or anti-resonant frequency in the electronic part **1A** including the circuit (load) that is supplied with power or a circuit including the electronic part **1A** electrically connected to a different electronic part.

That is, switching of connection between the electrodes **11b** and **12b** and the power supply line **32** by the switching section **20** in the electronic part **1A** allows change in the source impedance, the anti-resonant frequency, and the like of the electronic part **1A** or the circuit including the electronic part **1A**.

In order to change the source impedance, the anti-resonant frequency, and the like by the switching section **20** through switching connection to the power supply line **32**, the electrodes **11b** and **12b** may be made different in diameter, as in FIG. 1A, or may be made different in distance from the electrode **13b**, as in FIG. 1B.

In the electronic part **1B** illustrated in FIG. 1B, the distances of the electrodes **11b** and **12b** equal in diameter from the electrode **13b** are different from each other (the distance **L1** < a distance **L2**). The thicknesses of the insulat-

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ing films **14** that cover the side surfaces of the electrodes **11b** and **12b** are assumed to be equal in the example in FIG. **1B**. In the electronic part **1B**, the capacitance **C1** between the electrodes **11b** and **13b** and a capacitance **C2** between the electrodes **12b** and **13b** are different from each other. The electronic part **1B** in FIG. **1B** is different from the electronic part **1A** in FIG. **1A** in the above-described respects.

In the electronic part **1B** as well, the source impedance, the anti-resonant frequency, and the like of the electronic part **1B** or a circuit including the electronic part **1B** are changed by connecting one or both of the electrodes **11b** and **12b** to the power supply line **32** using the switches **21** and **22** of the switching section **20**.

The present disclosure is not limited to the examples in FIGS. **1A** and **1B**. The structure (permittivity) of a dielectric between electrodes may be changed in advance by previously providing electrodes different in diameter, providing electrodes different in interelectrode distance, making the thicknesses of the insulating films **14** different, or performing something else at the substrate **10**. Switching of connection between electrodes in various forms and the power supply line **32** using the switching section **20** allows control of the source impedance, the anti-resonant frequency, and the like of an electronic part or a circuit including the electronic part and achievement of satisfactory power integrity.

Additionally, with the configuration of an electronic part or a circuit including the electronic part, it is possible to switch an electrode to connect to the power supply line **32** and achieve a desired source impedance, a desired anti-resonant frequency, and the like. This allows obviation of the necessity for redesign and remanufacture of an electronic part or an electronic device using the electronic part.

At a time of manufacture, structural variation which may affect power source characteristics, such as a source impedance and an anti-resonant frequency, may occur between different electronic parts or electronic devices. The above-described technique accommodates variation in power source characteristics due to the above-described manufacturing variation between electronic parts or electronic devices through connection switching by the switching section **20**.

When a source impedance or the like is to be controlled using a bypass capacitor, there may be no installation place for the bypass capacitor or an installation place may be too separate from a target electronic part to achieve sufficient effects, depending on the configuration of an electronic part or an electronic device. The above-described technique involves switching connection between electrodes provided within the substrate **10** of an electronic part by the switching section **20** and is thus capable of controlling a source impedance and the like in the immediate vicinity of a load within the electronic part.

A case has been illustrated where connection between electrodes provided in the substrate **10** and the power supply line **32** is switched. Instead of or in addition to connection between electrodes and the power supply line **32**, connection between electrodes in various forms provided in the substrate **10** and the GND line **31** may be switched. Even by switching connection to the GND line **31**, it is possible to control the source impedance, the anti-resonant frequency, and the like of an electronic part or a circuit including the electronic part.

In the above-described examples, an electrode connected to the GND line **31** and an electrode connected to the power supply line **32** are arranged adjacent to each other. The electrodes do not have to be arranged adjacent to each other.

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Electrodes connected to the GND line **31** may be arranged adjacent to each other or electrodes connected to the power supply line **32** may be arranged adjacent to each other. It is possible to switch connection of such a group of electrodes by the switching section **20**.

A semiconductor chip has been given as an example of an electronic part. An interposer including the substrate **10** and the switching section **20** described above may be adopted as an electronic part.

A second embodiment will be described. The second embodiment will be described in the context of an electronic device including a plurality of stacked semiconductor chips.

FIGS. **2A** and **2B** are diagrams illustrating examples of an electronic device according to a second embodiment. FIGS. **2A** and **2B** schematically illustrate examples of the configuration of the electronic device according to the second embodiment.

An electronic device **40A** illustrated in FIG. **2A** includes a circuit board **50**, such as a printed circuit board, and a plurality of semiconductor chips which are mounted on the circuit board **50**. By way of example, the electronic device **40A** includes two semiconductor chips, a semiconductor chip **60** and a semiconductor chip **70** stacked thereon. The lower semiconductor chip **60** is electrically connected to the circuit board **50** through bumps **81** of solder or the like. Conductive sections for electrical continuity between a side where bumps **81** are disposed and a side where the upper semiconductor chip **70** is disposed are provided in the lower semiconductor chip **60** using TSV technology or an equivalent technology. The upper semiconductor chip **70** is electrically connected to the lower semiconductor chip **60** through the conductive sections of the lower semiconductor chip **60** and bumps **82** of solder or the like.

An electronic device **40B** illustrated in FIG. **2B** has a structure in which an interposer **90** is interposed between a layered product composed of the semiconductor chip **60** and the semiconductor chip **70** and the circuit board **50**. The lower semiconductor chip **60** is electrically connected to the interposer **90** through the bumps **81**. The interposer **90** is electrically connected to the circuit board **50** through bumps **83** of solder or the like. Conductive sections for electrical continuity between a side where the bumps **83** are disposed and a side where the semiconductor chip **60** is disposed are provided in the interposer **90**. The semiconductor chips **60** and **70** and the circuit board **50** are electrically connected to each other via the interposer **90** including the above-described conductive sections.

Examples of the configuration of the semiconductor chips **60** and **70** included in each of the electronic devices **40A** and **40B** as described above will be described.

FIGS. **3** and **4** are diagrams illustrating a first example of semiconductor chips according to the second embodiment. FIGS. **3** and **4** schematically illustrate configurations of a main portion of the lower semiconductor chip **60** and the upper semiconductor chip **70** in the first example.

The lower semiconductor chip **60** illustrated in FIG. **3** includes, for example, an Si substrate **110** and a switching section **120**. A compound semiconductor substrate of silicon germanium (SiGe), silicon carbide (SiC), gallium nitride (GaN), or the like may be used as the semiconductor chip **60**.

The Si substrate **110** has through-holes extending between principal surfaces thereof. By way of example, the Si substrate **110** has three through-holes, a through-hole **111a**, a through-hole **112a**, and a through-hole **113a**. A TSV **111b**, a TSV **112b**, and a TSV **113b** for electrical continuity between the principal surfaces of the Si substrate **110** are provided in the through-holes **111a**, **112a**, and **113a**, respec-



tively, using Cu or the like. Side surfaces of the TSVs 111b, 112b, and 113b are covered with insulating films (dielectric films) 114, respectively. FIGS. 3 and 4 illustrate a case where the TSVs 111b, 112b, and 113b are different in diameter from each other, and the insulating films 114 that cover the side surfaces are different in thickness from each other.

In the example in FIG. 3, of the TSVs 111b, 112b, and 113b, the TSV 111b smallest in diameter has a resistance R1 and an inductance L1. The TSV 112b largest in diameter has a resistance R2 and an inductance L2. The TSV 113b has a resistance R3 and an inductance L3.

In the example in FIG. 3, a capacitance between the TSV 111b and the Si substrate 110 is denoted by C1; a capacitance between the TSV 112b and the Si substrate 110 is denoted by C4; and a capacitance between the TSV 113b and the Si substrate 110 is denoted by C7. The capacitance of a portion of the insulating film 114 between the TSVs 111b and 113b is denoted by C3; the capacitance of a portion of the Si substrate 110 is denoted by C2; and the conductance of the portion is denoted by G. The capacitance of a portion of the insulating film 114 between the TSVs 112b and 113b is denoted by C6; the capacitance of a portion of the Si substrate 110 is denoted by C5; and the conductance of the portion is denoted by G.

The TSVs 111b, 112b, and 113b are electrically connected to a circuit (load) (not illustrated) including a transistor or the like. The TSVs 111b, 112b, and 113b are also electrically connected to the switching section 120.

The switching section 120 includes a switch 121 and a switch 122 which are each composed of a semiconductor switch or the like. For example, a semiconductor switch may be implemented using a semiconductor substrate (the Si substrate 110) used in the semiconductor chip 60 and a wiring layer which is provided on the semiconductor substrate. The operation of the switches 121 and 122 is controlled using a control section (a switch control section 125 (to be described later), for example) which is electrically connected to the switches 121 and 122. The switching section 120 of the lower semiconductor chip 60 is electrically connected to the upper semiconductor chip 70 via the bumps 82.

The upper semiconductor chip 70 includes, for example, the Si substrate 110, like the lower semiconductor chip 60. The TSVs 111b, 112b, and 113b provided in the Si substrate 110 are electrically connected to a circuit (load) (not illustrated) including a transistor or the like.

The circuit board 50 in FIG. 2A or the circuit board 50 and the interposer 90 in FIG. 2B have a GND line 131 which is set at a ground potential GND and a power supply line 132 which is set at a power potential Vcc during operation of the electronic device 40A or 40B. In the above-described layered product composed of the semiconductor chips 60 and 70, for example, the TSVs 113b of both the Si substrates 110 are electrically connected to the GND line 131. The TSVs 111b and 112b of the lower semiconductor chip 60 are electrically connected to the respective power supply lines 132.

The switching section 120 of the lower semiconductor chip 60 switches between connection of the TSV 111b of the lower semiconductor chip 60 to one or both of the TSVs 111b and 112b of the upper semiconductor chip 70 and disconnection of the TSV 111b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122. The switching section 120 of the lower semiconductor chip 60 also switches between connection of the TSV 112b of the lower semiconductor chip 60 to one or both of the TSVs

111b and 112b of the upper semiconductor chip 70 and disconnection of the TSV 112b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122.

That is, if the switching section 120 connects the TSV 111b of the lower semiconductor chip 60 to the TSV 111b of the upper semiconductor chip 70, the upper and lower TSVs 111b connected in series are connected to the power supply line 132. If the switching section 120 connects the TSV 111b of the lower semiconductor chip 60 to the TSV 112b of the upper semiconductor chip 70, the lower TSV 111b and the upper TSV 112b connected in series are connected to the power supply line 132. If the switching section 120 connects the TSV 111b of the lower semiconductor chip 60 to the TSVs 111b and 112b of the upper semiconductor chip 70, the lower TSV 111b and the upper TSVs 111b and 112b connected in parallel are connected to the power supply line 132.

Similarly, if the switching section 120 connects the TSV 112b of the lower semiconductor chip 60 to the TSV 111b of the upper semiconductor chip 70, the lower TSV 112b and the upper TSV 111b connected in series are connected to the power supply line 132. If the switching section 120 connects the TSV 112b of the lower semiconductor chip 60 to the TSV 112b of the upper semiconductor chip 70, the upper and lower TSVs 112b connected in series are connected to the power supply line 132. If the switching section 120 connects the TSV 112b of the lower semiconductor chip 60 to the TSVs 111b and 112b of the upper semiconductor chip 70, the lower TSV 112b and the upper TSVs 111b and 112b connected in parallel are connected to the power supply line 132.

Note that, like the case where the lower TSV 111b and the upper TSV 112b are connected and the case where the lower TSV 112b and the upper TSV 111b are connected, cases may be the same in the types of combined TSVs. Note that even the cases may differ in source impedance and the like depending on the positional relationship with a circuit element present between the TSVs 111b and 112b or the loads supplied with power.

A case has been illustrated where the Si substrates 110 provided with the same TSVs 111b, 112b, and 113b are used in the upper semiconductor chip 70 and the lower semiconductor chip 60. Alternatively, the Si substrates 110 with TSVs different in diameter, coating insulating film thickness, or the like may, of course, be used in the upper semiconductor chip 70 and the lower semiconductor chip 60.

The above-described TSV connection switching by the switching section 120 changes the configuration (equivalent circuit) of a circuit including the power supply line 132 and the GND line 131. The source impedance, the anti-resonant frequency, and the like of the semiconductor chip 60 or 70 or the electronic device 40A or 40B are controlled so as to have desired values or fall within desired ranges by controlling switching by the switching section 120 so as to achieve a desired form of TSV connection. This allows achievement of satisfactory power integrity.

Since switching among TSVs provided in the Si substrates 110 of the semiconductor chips 60 and 70 is performed by the switching section 20, it is possible to control the source impedance and the like in the immediate vicinity of the load within the semiconductor chip 60 or 70.

Additionally, since switching by the switching section 120 is capable of controlling a source impedance, an anti-resonant frequency, and the like, it is possible to obviate the necessity for redesign and remanufacture of the semiconductor chips 60 and 70 and optionally the circuit board 50

and the interposer 90. It is also possible to accommodate variation in source impedance, anti-resonant frequency, and the like due to manufacturing variation between the semiconductor chips 60 and between the semiconductor chips 70 and optionally between the circuit boards 50 and between the interposers 90.

Note that a case has been illustrated where TSV connection on the power supply line 132 is switched. Instead of or in addition to the TSV connection on the power supply line 132, TSV connection on the GND line 131 may be switched. That is, the TSV 113b of the semiconductor chip 60 may be connected to the power supply line 132, and the switching section 120 may switch connection between the TSVs 111b and 112b and the GND line 131, as illustrated in, for example, FIG. 4. The TSV connection on the GND line 131 may be switched through use of the above-described approach, instead of or in addition to the TSV connection on the power supply line 132. This allows control of the source impedance, the anti-resonant frequency, and the like of an electronic part or a circuit including the electronic part.

A case has been illustrated as the first example where the switching section 120 is provided at the lower semiconductor chip 60, which switches TSV connection to the upper semiconductor chip 70. The switching section 120 may be provided at the upper semiconductor chip 70.

FIG. 5 is a diagram illustrating a second example of the semiconductor chips according to the second embodiment. FIG. 5 schematically illustrates a configuration of the main portion of the lower semiconductor chip 60 and the upper semiconductor chip 70 in the second example.

As illustrated in FIG. 5, the switching section 120 may be provided at the upper semiconductor chip 70. As described above, the switching section 120 includes the switches 121 and 122, such as a semiconductor switch. For example, a semiconductor switch may be implemented using a semiconductor substrate (the Si substrate 110, for example) used in the upper semiconductor chip 70 and a wiring layer which is provided on the semiconductor substrate.

The TSVs 111b and 112b of the lower semiconductor chip 60 are electrically connected to the power supply line 132, and the TSV 113b is electrically connected to the GND line 131. The switching section 120 of the upper semiconductor chip 70 switches between connection of the TSV 111b of the upper semiconductor chip 70 to one or both of the TSVs 111b and 112b of the lower semiconductor chip 60 and disconnection of the TSV 111b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122. The switching section 120 of the upper semiconductor chip 70 also switches between connection of the TSV 112b of the upper semiconductor chip 70 to one or both of the TSVs 111b and 112b of the lower semiconductor chip 60 and disconnection of the TSV 112b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122.

As described above, the switching section 120 provided at the upper semiconductor chip 70 is also capable of performing control such that a desired TSV connection is achieved. With this configuration, it is possible to control the source impedance, the anti-resonant frequency, and the like of the semiconductor chip 60 or 70 or the electronic device 40A or 40B so as to have desired values or fall within desired ranges and achieve satisfactory power integrity. It is also possible not only to obviate the necessity for redesign and remanufacture of the semiconductor chips 60 and 70 and the like but also to accommodate variation in source impedance, anti-resonant frequency, and the like due to manufacturing variation.

The above-described TSV connection switching by the switching section 120 may be performed between the semiconductor chip 60 and the interposer 90 in the electronic device 40B as in FIG. 2B, in addition to between the stacked semiconductor chips 60 and 70.

FIG. 6 is a diagram illustrating a third example of the semiconductor chips according to the second embodiment. FIG. 6 schematically illustrates a configuration of the main portion of the lower semiconductor chip 60 and the interposer 90 in the third example.

By way of example, FIG. 6 illustrates the interposer 90 that includes the TSVs 111b, 112b, and 113b and the insulating films 114 that cover side surfaces of the TSVs 111b, 112b, and 113b, like the Si substrate 110 of the semiconductor chip 60. The switching section 120 of the semiconductor chip 60 is electrically connected to the interposer 90 via the bumps 81. A compound semiconductor substrate of silicon germanium (SiGe), silicon carbide (SiC), gallium nitride (GaN), or the like may be used instead of the Si substrate 110.

The TSVs 111b and 112b of the interposer 90 are electrically connected to the power supply line 132, and the TSV 113b is electrically connected to the GND line 131. The switching section 120 of the semiconductor chip 60 switches between connection of the TSV 111b of the semiconductor chip 60 to one or both of the TSVs 111b and 112b of the interposer 90 and disconnection of the TSV 111b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122. The switching section 120 of the semiconductor chip 60 switches between connection of the TSV 112b of the semiconductor chip 60 to one or both of the TSVs 111b and 112b of the interposer 90 and disconnection of the TSV 112b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122.

Note that a case has been illustrated where the same TSVs 111b, 112b, and 113b are provided both in the semiconductor chip 60 and the interposer 90. Alternatively, TSVs different in diameter, coating insulating film thickness, or the like may, of course, be provided in the semiconductor chip 60 and the interposer 90.

As described above, the switching section 120 is capable of performing control such that a desired TSV connection is achieved between the semiconductor chip 60 and the interposer 90. With this configuration, it is possible to control the source impedance, the anti-resonant frequency, and the like of the semiconductor chip 60 or 70 or the electronic device 40B so as to have desired values or fall within desired ranges and achieve satisfactory power integrity. It is also possible not only to obviate the necessity for redesign and remanufacture of the semiconductor chips 60 and 70 and the like but also to accommodate variation in source impedance, anti-resonant frequency, and the like due to manufacturing variation.

Note that it is, of course, possible to perform TSV connection switching by the switching section 120 as in the second example, between the semiconductor chip 60 and the semiconductor chip 70 stacked thereon in the third example. This allows increase in the number of feasible forms (variations) of TSV connection and makes it easier to control a source impedance, an anti-resonant frequency, and the like so as to have desired values or fall within desired ranges.

Although TSV connection switching between different electronic parts, namely, between the semiconductor chips 60 and 70 or between the semiconductor chip 60 and the interposer 90 has been illustrated above, TSV connection switching may also be performed within one electronic part.

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FIG. 7 is a diagram illustrating a fourth example of the semiconductor chips according to the second embodiment. FIG. 7 schematically illustrates a configuration of the main portion of the semiconductor chip 60 in the fourth example.

As illustrated in FIG. 7, the switching section 120 electrically connects the TSVs 111b, 112b, and 113b in a given region 115A within the one semiconductor chip 60 and the TSVs 111b, 112b, and 113b in a different region 115B.

For example, the TSVs 111b and 112b in the region 115A are electrically connected to the power supply line 132, and the TSV 113b is electrically connected to the GND line 131. The switching section 120 switches between connection of the TSV 111b in the region 115A to one or both of the TSVs 111b and 112b in the region 115B and disconnection of the TSV 111b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122. The switching section 120 also switches between connection of the TSV 112b in the region 115A to one or both of the TSVs 111b and 112b in the region 115B and disconnection of the TSV 112b from the one or both of the TSVs 111b and 112b, by use of the switches 121 and 122.

Although the semiconductor chip 60 has been taken as an example, the same TSV connection switching is also possible in the semiconductor chip 70 that is provided with the switching section 120.

As described above, the switching section 120 is also capable of performing control such that a desired TSV connection is achieved within the one semiconductor chip 60 (or 70). With this configuration, it is possible to control the source impedance, the anti-resonant frequency, and the like of the semiconductor chip 60 (or 70) or the electronic device 40A or 40B so as to have desired values or fall within desired ranges and achieve satisfactory power integrity. It is also possible not only to obviate the necessity for redesign and remanufacture of the semiconductor chip 60 (or 70) and the like but also to accommodate variation in source impedance, anti-resonant frequency, and the like due to manufacturing variation.

Note that it is, of course, possible to perform TSV connection switching by the switching section 120 as in the second or third example, between the semiconductor chip 60 (or 70) having the configuration in the fourth example and a different electronic part (a semiconductor chip or an interposer). This allows increase in the number of feasible forms of TSV connection and makes it easier to control a source impedance, an anti-resonant frequency, and the like so as to have desired values or fall within desired ranges.

The operation of the switches 121 and 122 of the switching section 120 described above is controlled using the control section electrically connected to the switches 121 and 122.

FIG. 8 is a diagram for explaining an example of a switching section according to the second embodiment.

As illustrated in FIG. 8, the switching section 120 includes switches 124 (the switches 121, 122, and the like) which are each composed of a semiconductor switch or the like. Each switch 124 is electrically connected to the TSVs 111b, 112b, and 113b of the different Si substrates 110 or the TSVs 111b, 112b, and 113b in different regions within the single Si substrate 110. The switching section 120 is provided with the switch control section 125 that is electrically connected to the switches 124. The switch control section 125 controls the operation of each switch 124.

A switch control signal which is generated based on information, such as a target source impedance value, an undesirable anti-resonant frequency range, and the number of TSVs desired for power supply is input to the switch

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control section 125. A switch control signal is generated through, for example, source impedance analysis or the like of an electronic part or an electronic device including the switching section 120. The switch control section 125 controls the operation (turnon, turnoff, contact switching, and the like) of each switch 124 based on an input switch control signal.

Note that the TSVs 111b, 112b, and 113b illustrated in FIG. 8 are merely examples and that the switching section 120 is capable of switching among TSVs in various forms.

A third embodiment will next be described.

An example of a method for forming a substrate provided with various electrodes (TSVs) different in diameter, coating insulating film thickness, or the like as described above will be described as the third embodiment.

FIGS. 9A to 9C and 10A to 10C are diagrams for explaining an example of the substrate formation method according to the third embodiment. FIGS. 9A to 9C and 10A to 10C schematically illustrate a cross-section of a main portion in a substrate formation process.

As illustrated in FIG. 9A, a substrate 210, such as a Si substrate, is prepared. An element (not illustrated), such as a transistor, may be formed outside a region where an electrode (TSV) (to be described later) is to be formed, at the substrate 210 to be prepared. A compound semiconductor substrate of silicon germanium (SiGe), silicon carbide (SiC), gallium nitride (GaN), or the like may also be used as the substrate 210.

A through-hole 211a is formed at a predetermined point of the prepared substrate 210, as illustrated in FIG. 9B. The through-hole 211a may be formed using photolithography, etching technology, or the like. Note that a state in which the through-hole 211a as in FIG. 9B is formed may be obtained by forming a hole from one principal surface of the substrate 210 such that the hole does not extend through the substrate 210 and grinding the substrate 210 from the other principal surface until the hole is reached.

After the formation of the through-hole 211a, an insulating film (dielectric film) 214 is formed on the surfaces including an inner surface of the through-hole 211a of the substrate 210, as illustrated in FIG. 9C. The insulating film 214 may be formed by, for example, forming a silicon oxide (SiO) film using thermal oxidation if the substrate 210 is made of Si or the like. Alternatively, depositing an insulating material, applying and curing an insulating resin material, or the like may be used for the insulating film 214. The insulating film 214 is formed using an appropriate method such that a thickness inside the through-hole 211a has a predetermined value.

A through-hole 212a is formed at a predetermined point different from the point of the through-hole 211a of the substrate 210 after the formation of the insulating film 214, as illustrated in FIG. 10A. The through-hole 212a may be formed using photolithography, etching technology, or the like.

After the formation of the through-hole 212a, the insulating film 214 is further formed using thermal oxidation or the like such that thicknesses inside the through-holes 211a and 212a have a predetermined value, as illustrated in FIG. 10B. At this time, the insulating film 214 that is thicker is formed on the side of the through-hole 211a formed earlier, and the insulating film 214 that is thinner is formed on the side of the through-hole 212a formed later.

After the insulating film 214 is formed in the above-described manner, a conductive material is charged into open regions of the through-holes 211a and 212a to form an electrode 211b and an electrode 212b as illustrated in FIG.

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10C. For example, Cu or a material based on Cu may be used as the conductive materials for the electrodes **211b** and **212b**. The electrodes **211b** and **212b** may be formed by, for example, charging such a material into the open regions of the through-holes **211a** and **212a** using plating.

A case has been illustrated where the electrode **211b** that is covered with the thicker insulating film **214** and has a smaller diameter is formed on the side of the through-hole **211a** formed earlier, and the electrode **212b** that is covered with the thinner insulating film **214** and has a larger diameter is formed on the side of the through-hole **212a** formed later. The above-described method is capable of forming a through-hole having an opening size (diameter) which is set based on the diameter of an electrode to be formed and the thickness of an insulating film to cover the electrode in the substrate **210**. It is possible to form various electrodes different in diameter, coating insulating film thickness, or the like by appropriately setting the opening sizes of through-holes to be formed (FIGS. **9B** and **10A**) and the thicknesses of insulating films to be formed in the through-holes (FIGS. **9C** and **10B**).

FIGS. **11A** to **11D** and **12A** to **12D** are diagrams for explaining a different example of the substrate formation method according to the third embodiment. FIGS. **11A** to **11D** and **12A** to **12D** schematically illustrate a cross-section of a main portion in the substrate formation process.

In the method, as illustrated in FIG. **11A**, the through-holes **211a** and **212a** are first formed in the prepared substrate **210**. As illustrated in FIG. **11B**, the through-hole **212a** on one side is masked with a resist **300**. As illustrated in FIG. **11C**, the insulating film **214** is formed in the through-hole **211a** on the other side such that a thickness inside the through-hole **211a** has a predetermined value. After that, as illustrated in FIG. **11D**, the resist **300** is removed.

As illustrated in FIG. **12A**, the through-hole **211a** side is then masked with a resist **310**. As illustrated in FIG. **12B**, the insulating film **214** is formed in the through-hole **212a** on the other side such that a thickness inside the through-hole **212a** has a predetermined value. FIG. **12B** illustrates a case where the insulating film **214** is formed such that the thickness of the insulating film **214** formed later on the through-hole **212a** side is smaller than the thickness of the insulating film **214** formed earlier on the through-hole **211a** side.

After the formation of the insulating film **214**, the resist **310** is removed, as illustrated in FIG. **12C**. A conductive material is charged into open regions of the through-holes **211a** and **212a** to form the electrodes **211b** and **212b**, as illustrated in FIG. **12D**.

The method as illustrated in FIGS. **11A** to **11D** and **12A** to **12D** is also capable of forming various electrode different in diameter, coating insulating film thickness, or the like by appropriately setting the opening sizes of through-holes to be formed (FIG. **11A**) and the thicknesses of insulating films to be formed in the through-holes (FIGS. **11C** and **12B**). The method is further capable of forming insulating films having predetermined thicknesses in respective through-holes under separate formation conditions and forming insulating films of different insulating materials in respective through-holes.

A fourth embodiment will be described.

An example of a method for controlling power source characteristics by switching the above-described electrode (TSV) connection using a switch-based switching section will be described as the fourth embodiment.

An electronic device (or a model of the electronic device) as illustrated in FIG. **13** is used in the present embodiment.

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FIG. **13** is a diagram illustrating an example of an electronic device according to the fourth embodiment.

An electronic device **400** illustrated in FIG. **13** includes a printed circuit board (PCB) **410**, an interposer **420**, a semiconductor chip **430**, and a semiconductor chip **440**.

The PCB **410** includes a GND plane **411** which is set at a ground potential GND, a power plane **412** which is set at a power potential Vcc, signal lines **413** serving as signal channels, and a through-hole **414** for electrical continuity in a PCB thickness direction. For example, a voltage regulator module (VRM) (not illustrated) is connected to the PCB **410**.

The interposer **420** is electrically connected to the PCB **410** using bumps **451**. The interposer **420** includes a GND wire **421** and a power supply wire **422** which are electrically connected to the GND plane **411** and the power plane **412**, respectively, of the PCB **410** and signal lines **423** (for a POS signal and a NEG signal) which are electrically connected to the signal lines **413** of the PCB **410**. A chip part **450**, such as a semiconductor chip or a chip capacitor, may be mounted on the interposer **420**.

The semiconductor chip **430** is electrically connected to the interposer **420** using bumps **452**. The semiconductor chip **430** includes a GND wire **431** and a power supply wire **432** which are electrically connected to the GND wire **421** and the power supply wire **422**, respectively, of the interposer **420** and signal lines **433** which are electrically connected to the signal lines **423** of the interposer **420**. The semiconductor chip **430** also includes TSVs **434** which are electrically connected to the GND wire **431** and the power supply wire **432**. Examples of the TSVs **434** include ones in various forms different in diameter, coating insulating film thickness, or the like as described above. A functional section, such as a network analyzer, for measuring impedance is embedded in the semiconductor chip **430**.

The semiconductor chip **440** is stacked on the lower semiconductor chip **430** and is electrically connected to the lower semiconductor chip **430** using bumps **453**. The semiconductor chip **440** includes a GND wire **441** and a power supply wire **442** which are electrically connected to the GND wire **431** and the power supply wire **432**, respectively, of the lower semiconductor chip **430** and signal lines **443** which are electrically connected to the signal lines **433** of the lower semiconductor chip **430**. The semiconductor chip **440** also includes TSVs **444** which are electrically connected to the GND wire **441** and the power supply wire **442**. Examples of the TSVs **444** include ones in various forms different in diameter, coating insulating film thickness, or the like as described above. A decoupling capacitor **445** and a circuit (load) **446** which consumes supplied power are electrically connected to the GND wire **441** and the power supply wire **442** of the semiconductor chip **440**. A serializer/deserializer (SERDES) circuit **447** is electrically connected to the signal lines **443** of the semiconductor chip **440**. A functional section, such as a network analyzer, for measuring impedance may be embedded in the semiconductor chip **440**.

The semiconductor chips **430** and **440** have the same configurations as those of the semiconductor chips **60** and **70** described in the second embodiment. A switching section including switches for switching connection among the TSVs **434** and **444** (and a switch control section which controls the operation of the switches) is (are) provided at one or both of the semiconductor chips **430** and **440**. A switching section (and a switch control section) as described in the second embodiment may be provided as the switching section (and the switch control section).

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Source impedance analysis is performed with a focus on, for example, a structural portion (indicated by a dotted frame X1 in FIG. 13) including the power lines (the power supply lines and the GND lines), to which the TSVs 434 and 444 are connected or from which the TSVs 434 and 444 are disconnected, of the electronic device 400 with the configuration as illustrated in FIG. 13. In the source impedance analysis, a model as illustrated in FIG. 14 which is a representation of the circuit configuration of the electronic device 400 (a real machine) may be used.

FIG. 14 is a diagram illustrating an example of an electronic device model according to the fourth embodiment.

A model 400a illustrated in FIG. 14 includes a VRM section 460a corresponding to the VRM of the electronic device 400, a PCB section 410a corresponding to the PCB 410, and an interposer section 420a corresponding to the interposer 420. The model 400a also includes a TSV section 430a which includes the TSVs 434 and 444, connection to which is switchable, and a load section 440a corresponding to the load 446 that is supplied with power. In FIG. 14, reference character R denotes a resistance; L denotes an inductance; and C denotes a capacitance.

Characteristics of the interposer section 420a and the TSV section 430a between the PCB section 410a and the load section 440a of the model 400a are expressible as S-parameters (transmission coefficients and reflection coefficients). The S-parameters may change through switching of connection among the TSVs (434 and 444) of the TSV section 430a. The S-parameters of the TSV section 430a may be acquired through a simulation using the model 400a or through measurement using a network analyzer in the electronic device 400. The use of the S-parameters allows obtainment of input and output source impedances of the TSV section 430a.

The flow of control of power source characteristics (a source impedance and an anti-resonant frequency) through source impedance analysis using the model 400a as described above of the electronic device 400 will be described.

FIG. 15 is a diagram illustrating an example of a source impedance analysis device used for power source characteristic control processing according to the fourth embodiment. FIGS. 16 and 17 are charts illustrating an example of the flow of the power source characteristic control processing according to the fourth embodiment.

For example, a source impedance analysis device 500 as illustrated in FIG. 15 is used for the power source characteristic control processing using the model 400a.

The source impedance analysis device 500 includes a power source characteristic control processing section 510 and a switch control signal generation section 520. The power source characteristic control processing section 510 performs a process of obtaining a combination of connections among TSVs (434 and 444) which achieves desired power source characteristics based on the source impedance and the like of the model 400a (or the electronic device 400). The switch control signal generation section 520 generates a switch control signal indicating the combination of TSV connections obtained by the power source characteristic control processing section 510.

The switch control signal generated by the switch control signal generation section 520 of the source impedance analysis device 500 is input to a switch control section 471 of a switching section 470 for TSV connection switching which is provided in the electronic device 400.

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At a time of control of power source characteristics, various settings used for source impedance analysis are first made (step S10 in FIG. 16). For example, a target source impedance (a target impedance  $Z_t$ ), an undesirable anti-resonant frequency range, and the number of TSVs desired for current (power) supply are set. Note that the target impedance  $Z_t$  may be calculated by expression (1) below.

$$Z_t = (V_{cc} \times \text{ripple percentage}) / (50\% \times I_{max}) \quad (1)$$

In expression (1),  $V_{cc}$  represents a source voltage, and  $I_{max}$  represents maximum current consumption.

The number of TSVs desired for current supply may be obtained by dividing the maximum current consumption by an allowable current for one TSV.

For the source impedance analysis, for example, an equivalent circuit (RLC circuit) of the model 400a of the electronic device 400 and a frequency characteristic which is acquired by electromagnetic field analysis of the electronic device 400 or actual measurement are prepared in addition to the settings.

For the source impedance analysis, an initial TSV (initial TSVs) to be connected to power lines (a power supply line and a GND line) is (are) selected (step S1 in FIG. 16). For example, among a group of TSVs, connection to which is switchable, a TSV which has a medium diameter or a TSV which has a medium capacitance between the TSV and an adjacent TSV is selected based on the number of TSVs desired for current supply.

For the source impedance analysis using the model 400a, the various pieces of setup information and information indicating the model 400a as described above are input to the power source characteristic control processing section 510 of the source impedance analysis device 500. The power source characteristic control processing section 510 selects, for example, a TSV which meets a predetermined condition as described above from among the group of TSVs, connection to which is switchable, using the information on the model 400a or the equivalent circuit.

The power source characteristic control processing section 510 connects the selected TSVs to the power lines (step S2 in FIG. 16). The power source characteristic control processing section 510 generates the model 400a that includes the TSV section 430a with the selected TSVs connected to the power lines and executes source impedance analysis processing using the pieces of information set earlier (step S3 in FIG. 16). The power source characteristic control processing section 510 executes a process of obtaining the S-parameters of the TSV section 430a in the generated model 400a when power is supplied within a predetermined frequency range and obtaining a source impedance before the load section 440a from the S-parameters.

An example of a source impedance characteristic obtained through the above-described processing is illustrated in FIG. 18. In the example in FIG. 18, anti-resonance is occurring near a frequency of  $10^6$  Hz. An impedance of  $0.1\Omega$  is the target impedance  $Z_t$ .

The power source characteristic control processing section 510 judges whether the source impedance obtained in step S3 is not more than the target impedance  $Z_t$  (step S4 in FIG. 16). If the source impedance obtained in step S3 is not more than the target impedance  $Z_t$ , it may be said that an appropriate source impedance has been achieved by connection between the selected TSVs and the power lines at a time of the source impedance analysis processing in step S3. If the obtained source impedance is not more than the target

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impedance  $Z_t$ , the power source characteristic control processing section 510 ends the power source characteristic control processing.

On the other hand, if the source impedance obtained in step S3 exceeds the target impedance  $Z_t$ , the power source characteristic control processing section 510 judges whether an anti-resonant frequency  $f_r$  is outside the undesirable anti-resonant frequency range set in advance (step S5 in FIG. 16). If the anti-resonant frequency  $f_r$  is outside the undesirable anti-resonant frequency range, the power source characteristic control processing section 510 ends the power source characteristic control processing.

In a certain case, the anti-resonant frequency  $f_r$  may be within the undesirable anti-resonant frequency range set in advance. For example, assuming that a range indicated by a dotted frame X2 in FIG. 18 is the undesirable anti-resonant frequency range set in advance, the anti-resonant frequency  $f_r$  is within the frequency range indicated by the dotted frame X2 in the example in FIG. 18. In this case, the power source characteristic control processing section 510 performs the processing below.

That is, the power source characteristic control processing section 510 first judges whether the anti-resonant frequency  $f_r$  is not more than a frequency at the center (a middle value) of the undesirable anti-resonant frequency range (the dotted frame X2 in FIG. 18) set in advance (step S6 in FIG. 17).

The anti-resonant frequency  $f_r$  is represented by following expression (2):

$$f_r = 1/[2\pi\sqrt{\{(L_p + L_t) \times (C_p \times C_t) / (C_p + C_t)\}}] \quad (2)$$

In expression (2),  $L_p$  represents the inductance of VG planes,  $C_p$  represents the capacitance of the VG planes,  $L_t$  represents the inductance of a TSV (TSVs), and  $C_t$  represents the capacitance of the TSV(s).

If the anti-resonant frequency  $f_r$  is not more than the middle value of the undesirable anti-resonant frequency range in step S6, the power source characteristic control processing section 510 selects a TSV (TSVs) whose inductance  $L_t$  and capacitance  $C_t$  form a larger product when multiplied together such that the anti-resonant frequency  $f_r$  is lower (step S7 in FIG. 17). For example, the power source characteristic control processing section 510 selects a TSV (TSVs) which has (have) a capacitance  $C_t$  about twice that of the TSV(s) selected at a time of the acquisition of the anti-resonant frequency  $f_r$ .

Note that, at a time of the selection, selection may be performed so as to, for example, switch from one TSV selected earlier to a plurality of TSVs or switch from a plurality of TSVs selected earlier to one TSV in order to make the anti-resonant frequency  $f_r$  lower. Alternatively, selection may be performed so as to switch from a plurality of TSVs selected earlier to a plurality of TSVs.

If the anti-resonant frequency  $f_r$  exceeds the middle value of the undesirable anti-resonant frequency range in step S6, the power source characteristic control processing section 510 selects a TSV (TSVs) whose inductance  $L_t$  and capacitance  $C_t$  form a smaller product when multiplied together such that the anti-resonant frequency  $f_r$  is higher (step S8 in FIG. 17). For example, the power source characteristic control processing section 510 selects a TSV (TSVs) which has (have) a capacitance  $C_t$  about one-half of that of the TSV(s) selected at the time of the acquisition of the anti-resonant frequency  $f_r$ .

Note that, at a time of the selection, selection may be performed so as to, for example, switch from one TSV selected earlier to a plurality of TSVs or switch from a plurality of TSVs selected earlier to one TSV in order to

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make the anti-resonant frequency  $f_r$  higher. Alternatively, selection may be performed so as to switch from a plurality of TSVs selected earlier to a plurality of TSVs.

After the above-described selection, the power source characteristic control processing section 510 returns to step S2. The power source characteristic control processing section 510 switches from the TSV(s) connected to the power lines to the TSV(s) selected in step S7 or S8 and executes the processes in step S3 and the subsequent steps. The power source characteristic control processing section 510 repeatedly executes the processes in steps S2 to S8 until the source impedance becomes not more than target impedance  $Z_t$  or the anti-resonant frequency  $f_r$  falls outside the undesirable range.

In this case, in step S7 for a second or further time, values of an inductance  $L_t$  and a capacitance  $C_t$  which a TSV (TSVs) to be selected is (are) desired to have may be changed in accordance with the difference between the acquired anti-resonant frequency  $f_r$  and a lower limit of the undesirable anti-resonant frequency range. For example, if the difference between the acquired anti-resonant frequency  $f_r$  and the lower limit of the undesirable anti-resonant frequency range is large, a TSV (TSVs) whose inductance  $L_t$  and capacitance  $C_t$  are about four times initial values is (are) selected. On the other hand, if the difference is small, a TSV (TSVs) whose inductance  $L_t$  and capacitance  $C_t$  are about twice or three times the initial values is (are) selected.

In step S8 for a second or further time, values of an inductance  $L_t$  and a capacitance  $C_t$  which a TSV (TSVs) to be selected is (are) desired to have may be changed in accordance with the difference between the acquired anti-resonant frequency  $f_r$  and an upper limit of the undesirable anti-resonant frequency range. For example, if the difference between the acquired anti-resonant frequency  $f_r$  and the upper limit of the undesirable anti-resonant frequency range is large, a TSV (TSVs) whose inductance  $L_t$  and capacitance  $C_t$  are about one-fourth of the initial values is (are) selected. On the other hand, if the difference is small, a TSV (TSVs) whose inductance  $L_t$  and capacitance  $C_t$  are about one-half or one-third of the initial values is (are) selected.

The power source characteristic control processing section 510 obtains a combination of TSV connections which allows the source impedance to be not more than the target impedance  $Z_t$  or the anti-resonant frequency  $f_r$  to fall outside the undesirable range by executing the processes in steps S1 to S8 described above.

Note that the TSV connection switching has been illustrated in the context of the TSVs 434 and 444 of the semiconductor chips 430 and 440 of the electronic device 400 corresponding to the model 400a. Alternatively, TSVs may also be provided in the interposer 420, and TSV connection switching may be performed through the above-described source impedance analysis using a model including the TSVs.

After the above-described power source characteristic control processing, a switch control signal indicating a combination of TSV connections obtained through the processing is generated by the switch control signal generation section 520 of the source impedance analysis device 500. The generated switch control signal is input to the switch control section 471 of the switching section 470 provided in the electronic device 400. In the electronic device 400, the operation of each switch of the switching section 470 is controlled in accordance with the switch control signal input to the switch control section 471, and a TSV connection is made in the combination obtained through the power source

characteristic control processing. This leads to achievement of the electronic device **400** with satisfactory power integrity.

In the electronic device **400** with a TSV connection in a combination based on the power source characteristic control processing, it is possible to, for example, actually supply predetermined power, measure the S-parameters using an embedded network analyzer, and obtain the source impedance using the measured S-parameters.

Processing is performed in accordance with the example of the flow in FIGS. **16** and **17**. If an actually obtained source impedance is not more than the target impedance  $Z_t$  (step **S4** in FIG. **16**), a combination of TSV connections selected at this time is confirmed. If the actually obtained source impedance exceeds the target impedance  $Z_t$ , and the anti-resonant frequency  $f_r$  is outside the undesirable anti-resonant frequency range (step **S5** in FIG. **16**), the combination of TSV connections at this time is confirmed.

If the actually obtained source impedance exceeds the target impedance  $Z_t$ , and the anti-resonant frequency  $f_r$  is within the undesirable anti-resonant frequency range (step **S5** in FIG. **16**), a switch control signal for TSV connection switching is prepared in accordance with the value of the anti-resonant frequency  $f_r$  (steps **S6** to **S8** in FIG. **16**). The switch control signal is input to the switch control section **471** of the switching section **470** to control the operation of each switch, thereby performing TSV connection switching. For the electronic device **400** that has undergone the above-described TSV connection switching, an actual source impedance is obtained again in the above-described manner. The series of procedures are repeated until a combination of TSV connections, in which the actual source impedance is not more than the target impedance  $Z_t$  or the anti-resonant frequency  $f_r$  is outside the undesirable range, is obtained.

As described above, it is possible to produce the electronic device **400** with satisfactory power integrity as a real machine by use of a result of the power source characteristic control processing using the model **400a**.

The electronic device **400** as a real machine may have power source characteristics different from power source characteristics obtained for the model **400a** when the electronic device **400** is made to operate under actual operation conditions. In a case where there is manufacturing variation between the electronic devices **400** or electronic parts included in the electronic device **400**, such as the semiconductor chips **430** or **440**, the electronic device **400** as a real machine may similarly have power source characteristics different from the power source characteristics obtained for the model **400a**. Even in a case where a different electronic part is mounted on (shares the power lines with) the PCB **410** of the electronic device **400**, the same thing may happen. It is possible to implement the electronic device **400** that has satisfactory power integrity under actual operation conditions or the electronic device **400** that accommodates manufacturing variation by performing the above-described TSV connection switching in the electronic device **400** as a real machine, based on the source impedance and the like, as occasion arises. It is also possible to perform TSV connection switching later in accordance with the intended use of the electronic device **400**, control the power source characteristics such that the power source characteristics are fit for the intended use, and achieve satisfactory power integrity.

To perform the power source characteristic control processing through source impedance analysis using the model **400a**, as described above, the electronic device **400** as a real machine corresponding to the model **400a** do not have to be prepared (manufactured). For example, only the model **400a**

is created in advance based on specifications and the like before manufacture, the power source characteristic control processing is executed using the model **400a**, and information indicating a TSV connection, with which desired power source characteristics are achieved, is acquired in advance. The design and manufacture of the electronic device **400** are performed such that the electronic device **400** has the TSV connection indicated by the information. Production of the electronic device **400** satisfactory in power integrity is possible even by such a method.

Note that a processing function of the source impedance analysis device **500** may be implemented using a computer.

FIG. **19** is a diagram illustrating an example of the hardware configuration of a computer used as a source impedance analysis device.

A computer **600** is totally controlled by a processor **601**. A random access memory (RAM) **602** and a plurality of pieces of peripheral equipment are connected to the processor **601** via a bus **609**. The processor **601** may be a multiprocessor. The processor **601** is, for example, a central processing unit (CPU), a micro processing unit (MPU), a digital signal processor (DSP), an application specific integrated circuit (ASIC), or a programmable logic device (PLD). The processor **601** may be a combination of two or more elements of a CPU, an MPU, a DSP, an ASIC, and a PLD.

The RAM **602** is used as a main storage of the computer **600**. At least a portion of an operating system (OS) program or an application program to be executed by the processor **601** is temporarily stored in the RAM **602**. Various types of data desired for processing by the processor **601** are also stored in the RAM **602**.

The pieces of peripheral equipment connected to the bus **609** include a hard disk drive (HDD) **603**, a graphic processing unit **604**, an input interface **605**, an optical drive unit **606**, an equipment connection interface **607**, and a network interface **608**.

The HDD **603** magnetically writes data to or reads data from an internal disk. The HDD **603** is used as an auxiliary storage of the computer **600**. An OS program, an application program, and various types of data are stored in the HDD **603**. Note that a semiconductor storage, such as a flash memory, may be used as an auxiliary storage.

A monitor **611** is connected to the graphic processing unit **604**. The graphic processing unit **604** displays an image on a screen of the monitor **611** in accordance with an instruction from the processor **601**. Examples of the monitor **611** include a display device using a cathode ray tube (CRT) and a liquid display device.

A keyboard **612** and a mouse **613** are connected to the input interface **605**. The input interface **605** transmits a signal sent from the keyboard **612** or the mouse **613** to the processor **601**. Note that the mouse **613** is an example of a pointing device and that any other pointing device may be used instead. Other examples of a pointing device include a touch panel, a tablet, a touch pad, and a trackball.

The optical drive unit **606** reads data recorded in an optical disc **614** using laser light or the like. The optical disc **614** is a portable recording medium having data recorded thereon so as to be readable through light reflection. Examples of the optical disc **614** include a digital versatile disc (DVD), a DVD-RAM, a compact disc read only memory (CD-ROM), and a CD-recordable/rewritable (CD-R/RW).

The equipment connection interface **607** is a communication interface for connection of a piece of peripheral equipment to the computer **600**. For example, a memory unit

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615 or a memory reader/writer 616 may be connected to the equipment connection interface 607. The memory unit 615 is a recording medium which is equipped with a function of communication with the equipment connection interface 607. The memory reader/writer 616 is a device for data writing to a memory card 617 or data reading from the memory card 617. The memory card 617 is a card-type recording medium.

The network interface 608 is connected to a network 610. The network interface 608 performs transmission and reception of data to and from a different computer or communication equipment via the network 610.

The above-described hardware configuration allows implementation of the processing function of the source impedance analysis device 500.

The computer 600 implements the processing function of the source impedance analysis device 500 by, for example, executing a program recorded on a computer-readable recording medium. A program describing the details of processing to be executed by the computer 600 may be recorded on various recording media. For example, a program to be executed by the computer 600 may be stored in the HDD 603. The processor 601 loads at least a portion of the program in the HDD 603 into the RAM 602 and executes the program. A program to be executed by the computer 600 may also be recorded in a portable recording medium, such as the optical disc 614, the memory unit 615, or the memory card 617. A program stored in a portable recording medium becomes executable after being installed in the HDD 603 under control of the processor 601, for example. The processor 601 is also capable of executing a program while directly reading out the program from a portable recording medium.

All examples and conditional language recited herein are intended for pedagogical purposes to aid the reader in understanding the invention and the concepts contributed by the inventor to furthering the art, and are to be construed as being without limitation to such specifically recited examples and conditions, nor does the organization of such examples in the specification relate to a showing of the superiority and inferiority of the invention. Although the embodiments of the present invention have been described in detail, it should be understood that the various changes, substitutions, and alterations could be made hereto without departing from the spirit and scope of the invention.

What is claimed is:

1. An electronic part, comprising:
  - a substrate;
  - a first electrode configured to extend through the substrate and have a first opening size;
  - a second electrode configured to extend through the substrate and have a second opening size;
  - a plurality of switches configured to switch between direct connection of the first electrode to a first power line and direct connection of the second electrode to the first power line; and
  - a third electrode configured to extend through the substrate and be connected to a second power line different in potential from the first power line, a capacitance between the first and third electrodes and a capacitance between the second and third electrodes being different.
2. The electronic part according to claim 1, further comprising:
  - a first dielectric film configured to cover a side surface of the first electrode and has a first thickness; and

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a second dielectric film configured to cover a side surface of the second electrode and has a second thickness different from the first thickness.

3. The electronic part according to claim 1, wherein the first electrode is located at a first distance from the third electrode, and the second electrode is located at a second distance different from the first distance from the third electrode.
4. The electronic part according to claim 1, wherein the third electrode has a third opening size, the electronic part further comprises a fourth electrode that extends through the substrate and has a fourth opening size, there is a difference between a pair of the third and fourth opening sizes, a pair of a capacitance between the first and third electrodes and a capacitance between the first and fourth electrodes, a pair of a capacitance between the second and third electrodes and a capacitance between the second and fourth electrodes, or each pair of any combination of the pairs, and the plurality of switches switch between connection of the third electrode to the second power line and connection of the fourth electrode to the second power line.
5. The electronic part according to claim 1, wherein switching by the plurality of switches is performed based on a source impedance at a time of connection to the first and second power lines.
6. The electronic part according to claim 1, wherein switching by the plurality of switches is performed based on an anti-resonant frequency at a time of connection to the first and second power lines.
7. An electronic device, comprising:
  - a first electronic part, the first electronic part comprising a first substrate, a first power line provided at the first substrate, and a second power line different in potential from the first power line; and
  - a second electronic part, the second electronic part comprising a second substrate, a first electrode that extends through the second substrate and has a first opening size, a second electrode that extends through the second substrate and has a second opening size, a plurality of switches that switch between direct connection of the first electrode to the first power line and direct connection of the second electrode to the first power line, and a third electrode that extends through the second substrate and is connected to the second power line, the second electronic part having a difference between a pair of the first and second opening sizes, a pair of a capacitance between the first and third electrodes and a capacitance between the second and third electrodes, or each of the pairs.
8. The electronic device according to claim 7, wherein the third electrode has a third opening size, the second electronic part further includes a fourth electrode that extends through the second substrate and has a fourth opening size, there is a difference between a pair of the third and fourth opening sizes, a pair of a capacitance between the first and third electrodes and a capacitance between the first and fourth electrodes, a pair of a capacitance between the second and third electrodes and a capacitance between the second and fourth electrodes, or each pair of any combination of the pairs, and



the plurality of switches switch between connection of the third electrode to the second power line and connection of the fourth electrode to the second power line.

9. The electronic device according to claim 7, wherein the first power line includes a fifth electrode that extends through the first substrate, and the plurality of switches connect either one or both of the first and second electrodes to the fifth electrode.

10. The electronic part according to claim 1, wherein the plurality of switches are provided over the substrate.

11. An electronic device according to claim 7, wherein the plurality of switches are provided between the first substrate and the second substrate.

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